

## 75V Dual Phase, Advanced COT Buck Controller, Stackable for Multiphase Operation

### Features

- Input Voltage Range: 8V to 75V
- Input Down to 2V when  $V_{DD} = 5V$  from External Supply
- Adjustable Output Voltage from 0.6V to 28V
- Adaptive Constant On-Time Control:
  - High DeltaV™ operation
  - Any Capacitor™ stable
- 0.6V Internal Reference with  $\pm 1\%$  Accuracy
- Novel Ripple Injection Method to Allow Greater than 50% Duty Cycle Operation
- **Operates in CCM, Stackable for Multiphase Operation up to Eight Phases**
- Accurate Current Balancing Between Phases
- Accurate 180° Phasing of Outputs
- 100 kHz to 1 MHz Switching Frequency per Phase
- Secondary LDO to Improve System Efficiency
- Supports Start-up to Pre-Bias Output
- Remote Sense Amplifier for Tight Output Regulation
- **Droop Feature to Support Adaptive Voltage Positioning (AVP) for Improved Load Transient Response**
- Precision Enable Function for Low Standby Current
- External Programmable Soft Start to Reduce Inrush Current
- Lossless  $R_{DS(on)}$  Current Sensing with NTC Temperature Compensation or Resistor Sensing Method
- Programmable Current Limit and Hiccup Mode Short-Circuit Protection
- Thermal Shutdown with Hysteresis
- $-40^{\circ}\text{C}$  to  $+125^{\circ}\text{C}$  Junction Temperature Range
- Compact Size: 5 mm x 5 mm 32-Pin VQFN Package

### Applications

- Distributed Power Systems
- Communications/Networking Infrastructure
- Printers, Scanners, Graphic and Video Cards
- FPGA, CPU, Memory, GPU Core Supplies
- Automotive POL

### General Description

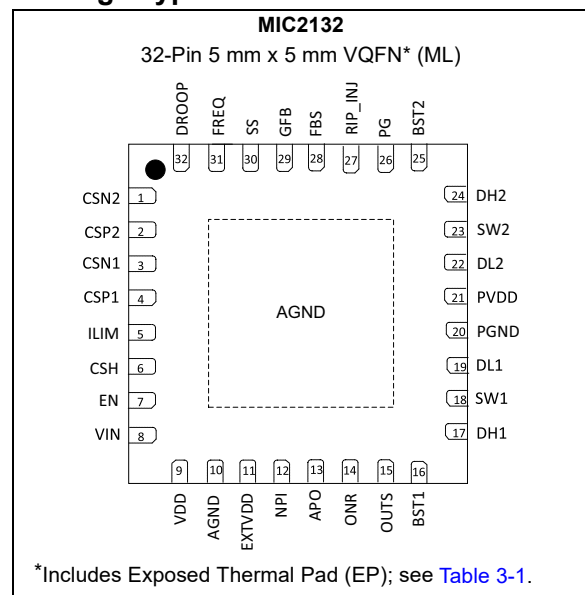
MIC2132 is a constant on-time, dual phase synchronous buck controller featuring a unique adaptive on-time control architecture with a stackable feature of up to eight phases. MIC2132 operates over an input supply range from 8V to 75V. The output voltage is adjustable down to 0.6V with an ensured accuracy of  $\pm 1\%$  at the FBS pin. The device operates with programmable switching frequency from 100 kHz to 1 MHz per phase.

The Hyper Speed Control® architecture supports ultrafast transient response under medium to heavy loads. The soft start is also programmable externally with a capacitor, thus enabling safe start-ups into heavy loads. MIC2132 has a remote sense amplifier for accurate output voltage control.

MIC2132 offers a full suite of protection features to ensure protection of the IC during Fault conditions. These include undervoltage lockout to ensure proper operation, programmable soft start to reduce inrush current, Hiccup mode short-circuit protection and thermal shutdown.

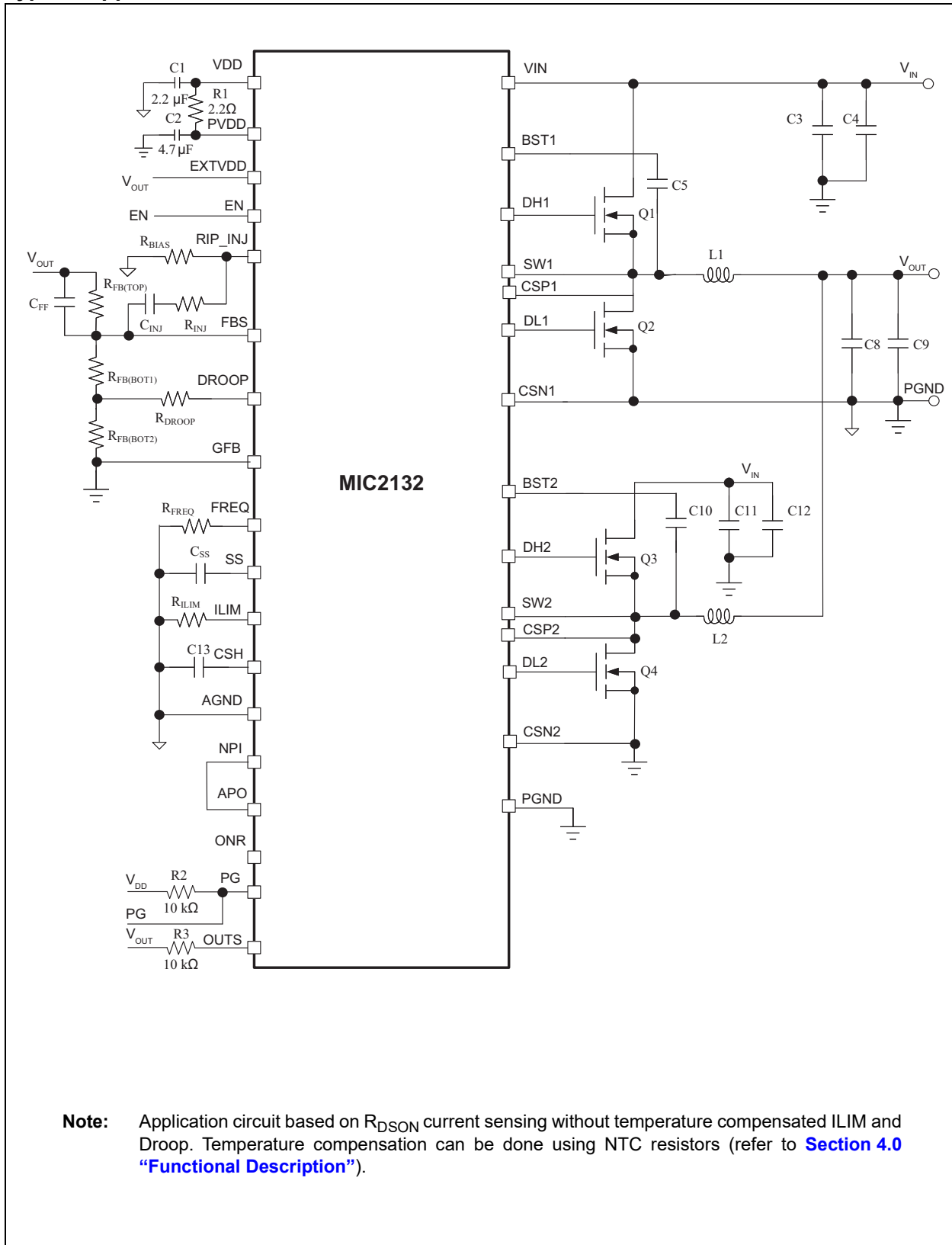
MIC2132 is available in a 32-pin, 5 mm x 5 mm VQFN package with a  $-40^{\circ}\text{C}$  to  $+125^{\circ}\text{C}$  operating junction temperature range.

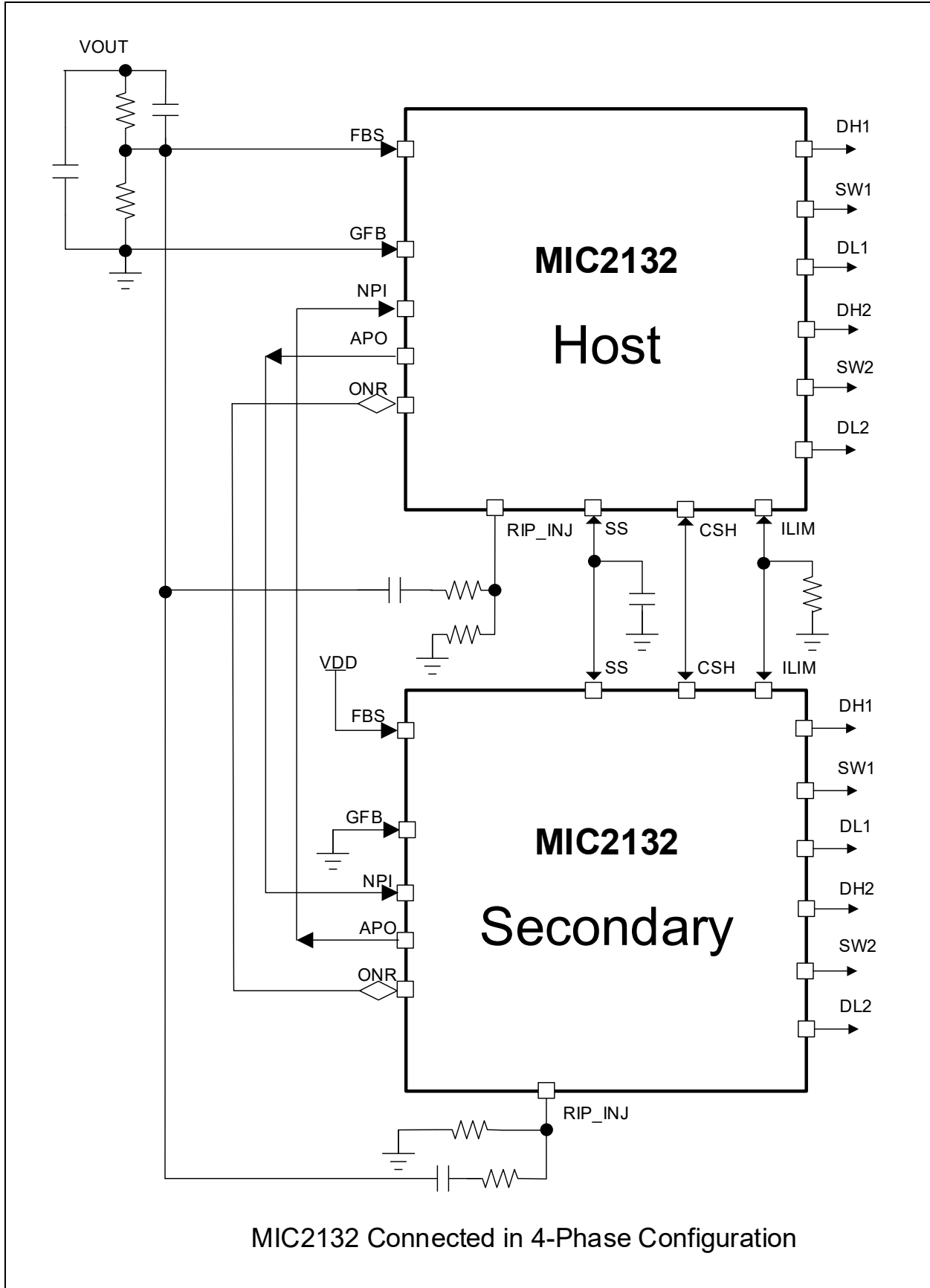
### Package Type



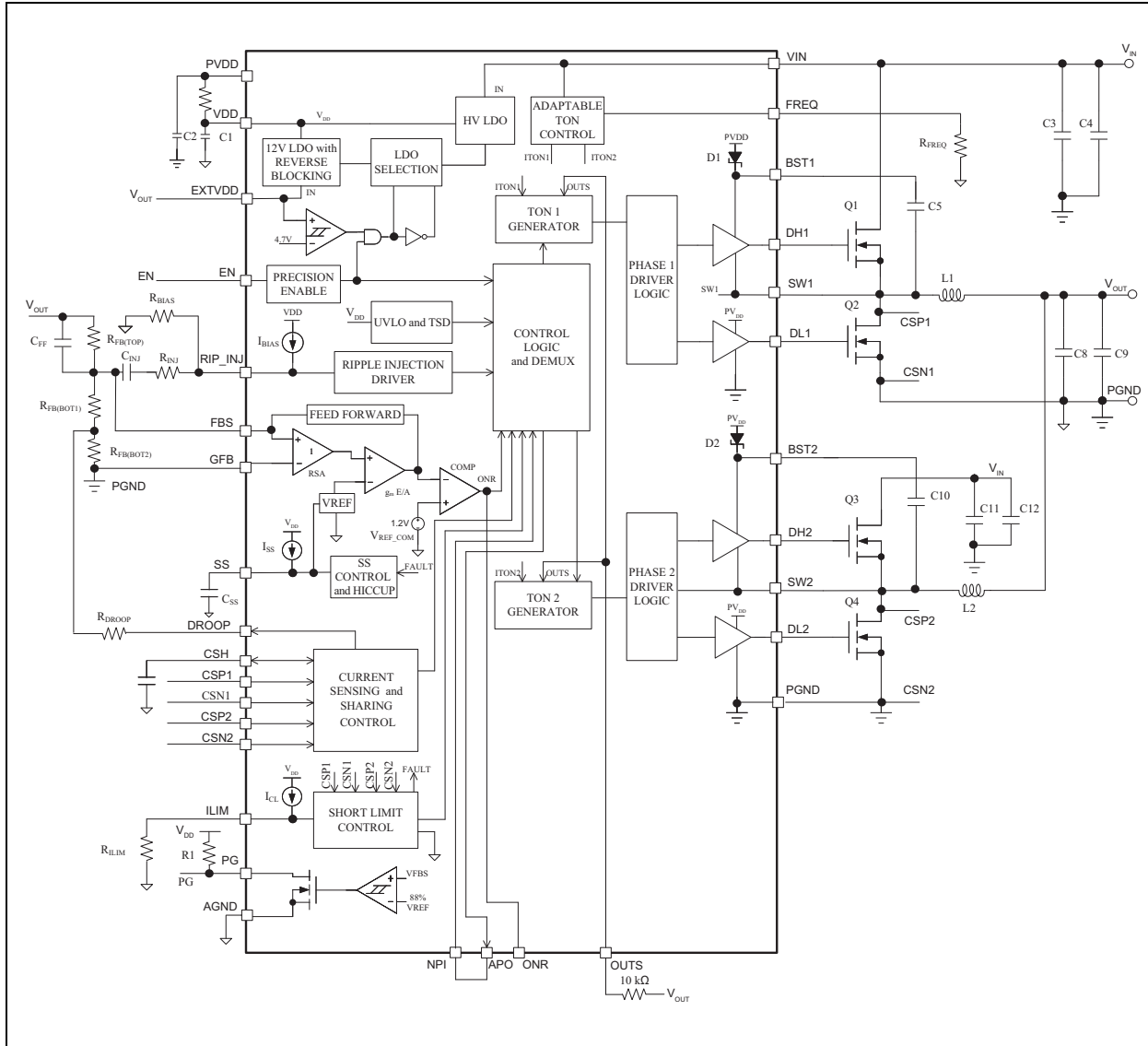
# MIC2132

## Typical Application Circuit





## Functional Block Diagram



## 1.0 ELECTRICAL CHARACTERISTICS

### Absolute Maximum Ratings<sup>†</sup>

$V_{IN}$ to PGND .....	-0.3V to +76V
$V_{DD}$ , OUTS to AGND .....	-0.3V to +6V
$PV_{DD}$ to PGND .....	-0.3V to +6V
EN to AGND .....	-0.3V to ( $V_{IN} + 0.3V$ )
SW1, SW2, CSP1, CSP2 to PGND .....	-0.3V to ( $V_{IN} + 0.3V$ )
BST1 to SW1, BST2 to SW2 .....	-0.3V to 6V
DH1 to SW1, DH2 to SW2 .....	-0.3V to ( $V_{BSTX} - V_{SWX} + 0.3V$ )
ILIM, FREQ, SS, RIP_INJ, FBS, DROOP, PG, CSH, NPI, APO, ONR to AGND .....	-0.3V to ( $V_{DD} + 0.3V$ )
EXTVDD to AGND .....	-0.3V to +14V
CSN1, CSN2, GFB, PGND to AGND .....	-0.3V to +0.3V
Maximum Junction Temperature ( $T_J$ ) .....	+150°C
Storage Temperature ( $T_S$ ) .....	-65°C to +150°C
Lead Temperature ( $T_{LEAD}$ ) .....	+300°C
ESD Rating <sup>(1)</sup> (HBM) .....	2000V
ESD Rating <sup>(1)</sup> (MM) .....	200V
ESD Rating <sup>(1)</sup> (CDM) .....	2000V

### Operating Ratings<sup>‡</sup>

Supply Voltage ( $V_{IN}$ ) .....	8V to 75V
$PV_{DD}$ , VDD Pin Voltage .....	4.5V to 5.5V
OUTS Pin Voltage .....	0.6V to 5.5V
EXTVDD Pin Voltage .....	0V to 13V
SW1, SW2, CSP1, CSP2 Pin Voltage .....	0V to $V_{IN}$
ILIM, FREQ, SS, RIP_INJ, FBS, DROOP, PG, CSH, NPI, APO, ONR to AGND .....	0V to $V_{DD}$
DL1, DL2 to AGND .....	0V to $V_{DD}$
DH1 to SW1, DH2 to SW2 .....	0V to $V_{DD}$
Enable Input Voltage ( $V_{EN}$ ) .....	0V to $V_{IN}$
Junction Temperature <sup>(2)</sup> ( $T_J$ ) .....	-40°C to +125°C

**† Notice:** Stresses above those listed under “**Absolute Maximum Ratings**” may cause permanent damage to the device. This is a stress rating only and functional operation of the device at those or any other conditions above those indicated in the operational sections of this specification is not intended. Exposure to maximum rating conditions for extended periods may affect device reliability

**‡ Notice:** The device is not ensured to function outside its operating ratings.

**Note 1:** Specification for packaged product only.

**2:**  $P_{D(MAX)} = (T_{J(MAX)} - T_A)/\theta_{JA}$ , where  $\theta_{JA}$  depends upon the printed circuit layout.

# MIC2132

## ELECTRICAL CHARACTERISTICS<sup>(1)</sup>

**Electrical Characteristics:**  $V_{IN} = 12V$ ;  $V_{OUT} = 5V$ ;  $f_{SW} = 500$  kHz/phase;  $V_{BST} - V_{SW} = 5V$ ;  $T_A = +25^\circ C$ , unless noted. **Boldface** values indicate  $-40^\circ C \leq T_J \leq +125^\circ C$ .

Parameters	Symbol	Min.	Typ.	Max.	Units	Conditions
<b>Power Supply Input</b>						
Input Voltage Range	$V_{IN}$	<b>8</b>	—	<b>75</b>	V	
Quiescent Supply Current	$I_Q$	—	5000	<b>8000</b>	$\mu A$	$V_{FBS} = +1.5V$
Shutdown Current	$I_{SD}$	—	25	<b>50</b>	$\mu A$	$V_{EN} = 0V$
<b>V<sub>DD</sub> and EXT<sub>VDD</sub></b>						
V <sub>DD</sub> Voltage Range	$V_{DD}$	<b>4.7</b>	5.1	<b>5.4</b>	V	$V_{IN} = 8V$ to $75V$ , $I_{VDD} = 20$ mA <b>(Note 5)</b>
V <sub>DD</sub> Undervoltage Lockout Upper Threshold	$V_{DDUV\_R}$	3.7	4.2	4.5	V	$V_{DD}$ rising
V <sub>DD</sub> UVLO Hysteresis	$V_{DDUV\_HYS}$	—	600	—	mV	Hysteresis
V <sub>DD</sub> Regulation	$\Delta V_{DD}$	—	1	<b>2.5</b>	%	$V_{IN} = 24V$ , $I_{VDD}$ from 1 mA to 40 mA <b>(Note 5)</b>
V <sub>DD</sub> Regulator Dropout Voltage	$V_{DROP\_VDD}$	—	0.8	1.05	V	$V_{IN} = 5.5V$ , $I_{VDD} = 25$ mA
EXT <sub>VDD</sub> Switchover Voltage	$V_{SO\_EVDD}$	<b>4.5</b>	4.7	<b>4.9</b>	V	$V_{IN} = 24V$ , EXT <sub>VDD</sub> rising, $I_{VDD} = 40$ mA
EXT <sub>VDD</sub> Switchover Voltage Hysteresis	$V_{SO\_HYS}$	—	250	—	mV	Hysteresis
EXT <sub>VDD</sub> Dropout Voltage	$V_{DROP\_EVDD}$	—	250	—	mV	$V_{EXTVDD} = 5V$ , $I_{VDD} = 40$ mA
EXT <sub>VDD</sub> Leakage Current	$I_{LK\_EVDD}$	—	0.1	—	$\mu A$	$V_{EXTVDD} = 14V$ , $V_{EN} = 0V$
<b>Soft Start</b>						
Soft Start Source Current	$I_{SS}$	0.8	1.2	1.7	$\mu A$	
<b>DC-DC Regulator</b>						
Output Voltage Adjustable Range	$V_{OUT}$	0.6	—	28	V	<b>Note 2</b>
<b>Reference and Remote Sensing Amplifier</b>						
Feedback Regulation Voltage	$V_{FBS\_GFB}$	<b>0.593</b>	0.6	<b>0.606</b>	V	Measured with EA in servo loop
FBS Bias Current	$I_{FBS}$	—	2	—	nA	$V_{FBS} = +0.6V$ <b>(Note 2)</b>
GFB Bias Current	$I_{GFB}$	—	12	—	$\mu A$	
Remote Sense Amplifier Gain	$G_{RSA}$	—	1.00	—	V/V	
<b>Enable</b>						
Enable Upper Threshold Voltage	$V_{EN\_TH}$	<b>1.05</b>	1.2	<b>1.36</b>	V	Enable rising
Enable Hysteresis	$V_{EN\_HYS}$	—	65	—	mV	
Enable Bias Current	$I_{EN}$	—	100	<b>200</b>	nA	$V_{EN} = 12V$

**Note 1:** Specification for packaged product only.

**2:** Guaranteed by design and characterization. Not production tested.

**3:** Measured in Test mode.

**4:** The maximum duty cycle is limited by the fixed mandatory off-time of typically 360 ns.

**5:** Limited by maximum junction temperature,  $T_J = +125^\circ C$ .

## ELECTRICAL CHARACTERISTICS<sup>(1)</sup> (CONTINUED)

**Electrical Characteristics:**  $V_{IN} = 12V$ ;  $V_{OUT} = 5V$ ;  $f_{SW} = 500$  kHz/phase;  $V_{BST} - V_{SW} = 5V$ ;  $T_A = +25^\circ C$ , unless noted. **Boldface** values indicate  $-40^\circ C \leq T_J \leq +125^\circ C$ .

Parameters	Symbol	Min.	Typ.	Max.	Units	Conditions
<b>On Timer</b>						
Nominal Switching Frequency per Phase	$f_{SWNOM\_PH}$	<b>400</b>	500	<b>600</b>	kHz	$V_{IN} = 12V$ , $V_{OUTS} = 5V$ , $R_{FREQ} = 40.2$ k $\Omega$
Minimum Switching Frequency per Phase	$f_{SWMIN\_PH}$	—	100	—	kHz	$V_{IN} = 12V$ , $V_{OUTS} = 5V$ , $R_{FREQ} = 200$ k $\Omega$
Maximum Switching Frequency per Phase	$f_{SWMAX\_PH}$	—	800	—	kHz	$V_{IN} = 12V$ , $V_{OUTS} = 5V$ , $R_{FREQ} = 25.5$ k $\Omega$
Minimum On-Time	$T_{ONMIN}$	—	60	—	ns	Measured in application ( <b>Note 2</b> )
Minimum Off-Time	$T_{OFFMIN}$	—	360	—	ns	$V_{FBS} = 0V$
Maximum Duty Cycle	$D_{MAX}$	—	85	—	%	$f_{SW} = 400$ kHz per phase ( <b>Note 4</b> )
Minimum Duty Cycle	$D_{MIN}$	—	0	—	%	$V_{FBS} = +1V$ ( <b>Note 2</b> )
<b>Current Limit</b>						
ILIM Source Current	$I_{CL}$	<b>8.3</b>	<b>9.6</b>	<b>10.56</b>	$\mu A$	
ILIM Source Current Temperature Coefficient	$TC_{ICL}$	—	0	—	ppm/ $^\circ C$	( <b>Note 2</b> )
Nominal Current Limit Threshold Voltage per Phase	$V_{ILIM\_TH}$	139	156	174	mV	$R_{ILIM} = 60.4$ k $\Omega$ ,
		—	47	—	mV	$R_{ILIM} = 105$ k $\Omega$ ,
		—	250	—	mV	$R_{ILIM} = 21$ k $\Omega$
Negative Current Limit Threshold Voltage	$V_{ILIM\_NTH}$	60	75	90	mV	$R_{ILIM} = 60.4$ k $\Omega$
<b>Current Sharing Amplifier</b>						
CSH Operating Point	$V_{CSH\_OP}$	<b>1.154</b>	<b>1.19</b>	<b>1.244</b>	V	$V_{CSN1} = V_{CSN2} = V_{CSP1} =$ $V_{CSP2} = 0V$
Current Sense Amplifier(s) Gain	$G_{CSA}$	—	8	—	V/V	As reflected on $V_{CSH}$ pin and DROOP pin
Current Sense Input Voltage Range	$V_{CS}$	<b>-120</b>	—	<b>+120</b>	mV	$-40^\circ C \leq T_J \leq +125^\circ C$
Phase to Phase Current Balance	$\Delta I_{PH}$	—	5	—	%	Using equal sense resistors on the bottom, equal inductances, $V_{OUT} = 5V$ , $f_{SW} = 500$ kHz, $V_{IN} = 12V$ , $V_{CSP1} - V_{CSN1} = -120$ mV, $V_{CSP2} - V_{CSN2} = -120$ mV
MIC2132 to MIC2132 Current Balance	$\Delta I_{PH\_DEV}$	—	8	—	%	In stacking applications

- Note 1:** Specification for packaged product only.  
**Note 2:** Guaranteed by design and characterization. Not production tested.  
**Note 3:** Measured in Test mode.  
**Note 4:** The maximum duty cycle is limited by the fixed mandatory off-time of typically 360 ns.  
**Note 5:** Limited by maximum junction temperature,  $T_J = +125^\circ C$ .

# MIC2132

## ELECTRICAL CHARACTERISTICS<sup>(1)</sup> (CONTINUED)

**Electrical Characteristics:**  $V_{IN} = 12V$ ;  $V_{OUT} = 5V$ ;  $f_{SW} = 500$  kHz/phase;  $V_{BST} - V_{SW} = 5V$ ;  $T_A = +25^\circ C$ , unless noted. **Boldface** values indicate  $-40^\circ C \leq T_J \leq +125^\circ C$ .

Parameters	Symbol	Min.	Typ.	Max.	Units	Conditions
<b>Adaptive Voltage Positioning (AVP), i.e., DROOP</b>						
$V_{DROOP}$ at No Load	$V_{DRP\_NLOAD}$	—	10	—	mV	Measure DROOP voltage ~ 0V when $V_{CSP1} - V_{CSN1} = 0V$ , $V_{CSP2} - V_{CSN2} = 0V$
$V_{DROOP}$ at Maximum Positive Range	$V_{DRP(PMAX)}$	—	0.96	—	V	Measure DROOP voltage ~1.2V when $V_{CSP1} - V_{CSN1} = -120$ mV, $V_{CSP2} - V_{CSN2} = -120$ mV
<b>Ripple Injection</b>						
Ripple Injection Pulse Width	$t_{PW(RI)}$	—	100	120	ns	
Ripple Injection Prepositioning Current	$I_{BIAS}$	—	4.8	6	$\mu A$	Force $V_{RIPINJ} = 0V$ , $V_{SS} = 0V$ , measure current
Injection Driver On-Resistance	$R_{DSON(INJ)}$	—	50	—	$\Omega$	
<b>Internal MOSFET Drivers</b>						
DHx On-Resistance, High State	$R_{ON\_DHH}$	—	2.5	4.5	$\Omega$	$I_{SOURCE} = 0.1A$
DHx On-Resistance, Low State	$R_{ON\_DHL}$	—	1.6	3.2	$\Omega$	$I_{SINK} = 0.1A$
DLx On-Resistance, High State	$R_{ON\_DLH}$	—	2.5	4.5	$\Omega$	$I_{SOURCE} = 0.1A$
DLx On-Resistance, Low State	$R_{ON\_DLL}$	—	0.8	1.5	$\Omega$	$I_{SINK} = 0.1A$
<b>SW, VIN and BST Leakage</b>						
BST Leakage	$I_{LEAK(BST)}$	—	—	10	$\mu A$	$V_{BST} = 75V$
VIN Leakage	$I_{LEAK(VIN)}$	—	—	60	$\mu A$	$V_{IN} = 70V$
SW Leakage	$I_{LEAK(SW)}$	—	—	20	$\mu A$	$V_{SW} = 70V$
<b>Power Good (PG)</b>						
PG Threshold from Low-to-High	$V_{PG\_TH}$	<b>83</b>	88	<b>94</b>	% $V_{OUT}$	$V_{FBS}$ rising
PG Threshold Hysteresis	$V_{PG\_HYS}$	—	7	—	% $V_{OUT}$	$V_{FBS}$ falling
PG Delay	$t_{D\_PG}$	—	100	—	$\mu s$	$V_{FBS}$ rising
PG Low State Voltage	$V_{PG\_L}$	—	70	<b>200</b>	mV	$V_{FBS} < 90\% \times V_{NOM}$ , $I_{PG} = 1$ mA
PG Leakage Current	$I_{LEAK(PG)}$	—	—	<b>500</b>	nA	$V_{PG} = 5.5V$

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**4:** The maximum duty cycle is limited by the fixed mandatory off-time of typically 360 ns.  
**5:** Limited by maximum junction temperature,  $T_J = +125^\circ C$ .



## ELECTRICAL CHARACTERISTICS<sup>(1)</sup> (CONTINUED)

**Electrical Characteristics:**  $V_{IN} = 12V$ ;  $V_{OUT} = 5V$ ;  $f_{SW} = 500$  kHz/phase;  $V_{BST} - V_{SW} = 5V$ ;  $T_A = +25^\circ C$ , unless noted. **Boldface** values indicate  $-40^\circ C \leq T_J \leq +125^\circ C$ .

Parameters	Symbol	Min.	Typ.	Max.	Units	Conditions
<b>Stackability APO, NPI, ONR</b>						
High-Level Input Voltage for NPI	$V_{IH(NPI)}$	2.0	—	—	V	Current = 0.5 mA
Low-Level Input Voltage for NPI	$V_{IL(NPI)}$	—	—	0.8	V	Current = 0.5 mA
High-Level Output Voltage for APO	$V_{OH(APO)}$	—	4.7	—	V	Current = 0.5 mA
Low-Level Output Voltage for APO	$V_{OL(APO)}$	—	0.25	—	V	Current = 0.5 mA
High-Level Output for ONR	$V_{OH(ONR)}$	—	4.5	—	V	Current = 0.5 mA
Low-Level Output for ONR	$V_{OL(ONR)}$	—	0.25	—	V	Current = 0.5 mA
Leakage Current	$I_{LEAK}$	—	—	1	$\mu A$	$V_{DD} = 5V$
ONR Short Current	$I_{SHT(ONR)}$	—	5.8	—	mA	
<b>Thermal Shutdown</b>						
Thermal Shutdown Threshold	$T_{SD}$	—	160	—	$^\circ C$	$T_J$ Rising ( <b>Note 2</b> )
Thermal Shutdown Hysteresis	$T_{SD\_HYS}$	—	20	—	$^\circ C$	<b>Note 2</b>

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## TEMPERATURE SPECIFICATIONS

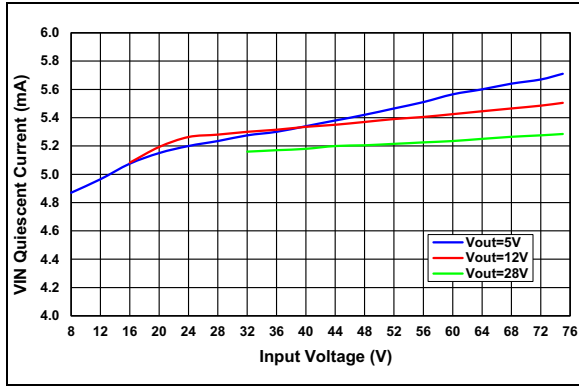
Parameters	Symbol	Min.	Typ.	Max.	Units	Conditions
<b>Temperature Ranges</b>						
Operating Junction Temperature Range	$T_J$	-40	—	+125	$^\circ C$	<b>Note 1</b>
Maximum Junction Temperature	$T_{J(ABSMAX)}$	—	—	+150	$^\circ C$	
Storage Temperature Range	$T_S$	-65	—	+150	$^\circ C$	
Lead Temperature	$T_{LEAD}$	—	—	+300	$^\circ C$	Soldering, 10s
<b>Package Thermal Resistance</b>						
Thermal Resistance, 5 mm x 5 mm, 32-Lead VQFN	$\theta_{JC}$	—	2	—	$^\circ C/W$	Junction to Case
Thermal Resistance, 5 mm x 5 mm, 32-Lead VQFN	$\theta_{JA}$	—	34	—	$^\circ C/W$	Junction to Ambient

**Note 1:** The maximum allowable power dissipation is a function of ambient temperature, the maximum allowable junction temperature and the thermal resistance from junction to air (i.e.,  $T_A$ ,  $T_J$ ,  $\theta_{JA}$ ). Exceeding the maximum allowable power dissipation will cause the device operating junction temperature to exceed the maximum +125 $^\circ C$  rating. Sustained junction temperatures above +125 $^\circ C$  can impact the device reliability.

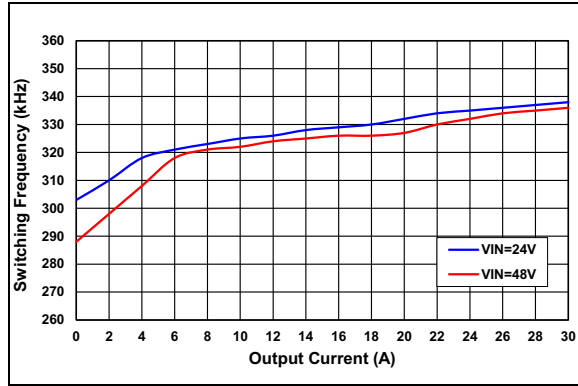
## 2.0 TYPICAL PERFORMANCE CURVES

**Note:** The graphs and tables provided following this note are a statistical summary based on a limited number of samples and are provided for informational purposes only. The performance characteristics listed herein are not tested or guaranteed. In some graphs or tables, the data presented may be outside the specified operating range (e.g., outside specified power supply range) and therefore, outside the warranted range.

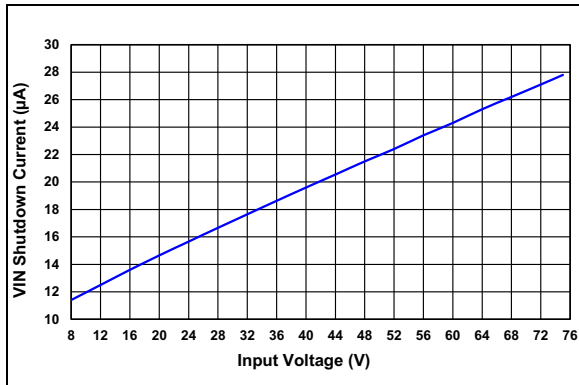
**Note:** Unless otherwise indicated,  $V_{IN} = 12V$ ;  $V_{OUT} = 5V$ ;  $f_{SW} = 500$  kHz/phase;  $V_{BST} - V_{SW} = 5V$ ;  $T_A = +25^\circ C$ .



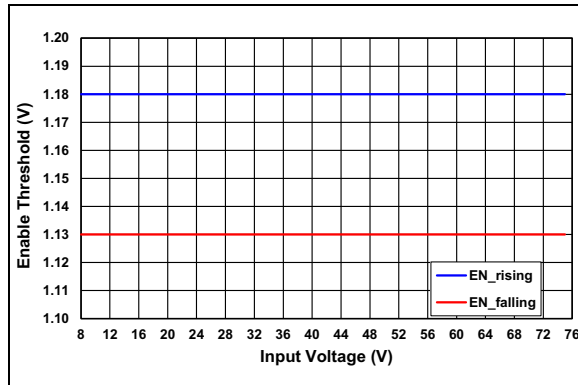
**FIGURE 2-1:**  $V_{IN}$  Quiescent Current vs. Input Voltage.



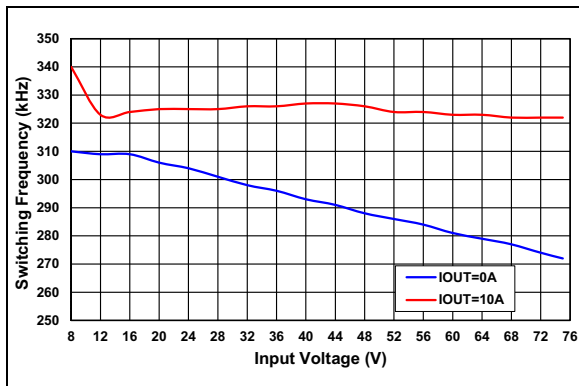
**FIGURE 2-4:** Switching Frequency vs. Output Current.



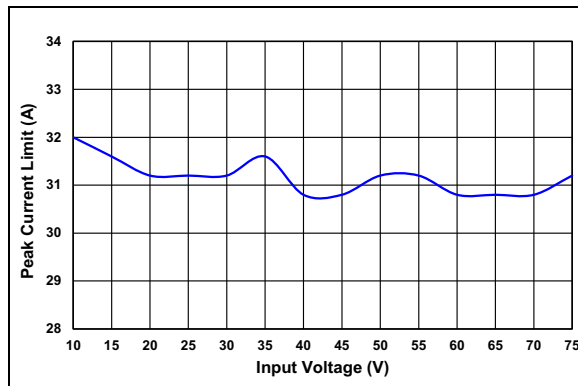
**FIGURE 2-2:**  $V_{IN}$  Shutdown Current vs. Input Voltage.



**FIGURE 2-5:** Enable Threshold vs. Input Voltage.

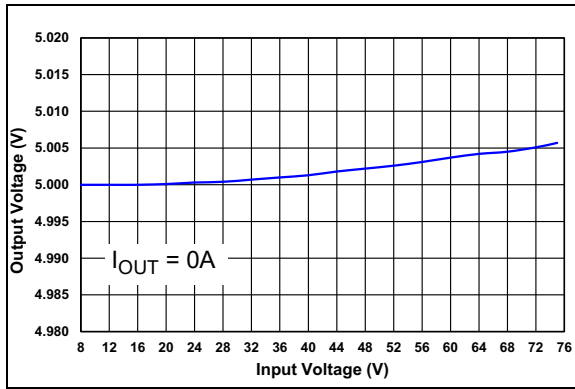


**FIGURE 2-3:** Switching Frequency vs. Input Voltage.

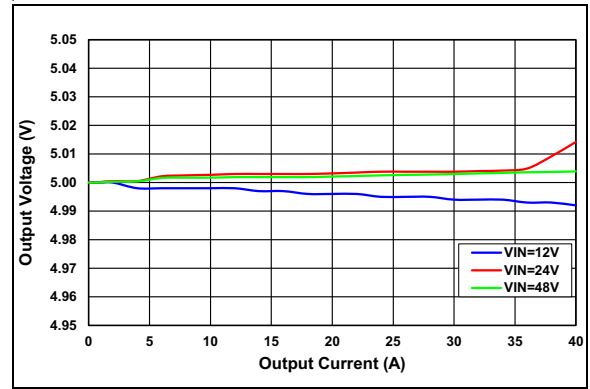


**FIGURE 2-6:** Peak Current Limit vs. Input Voltage.

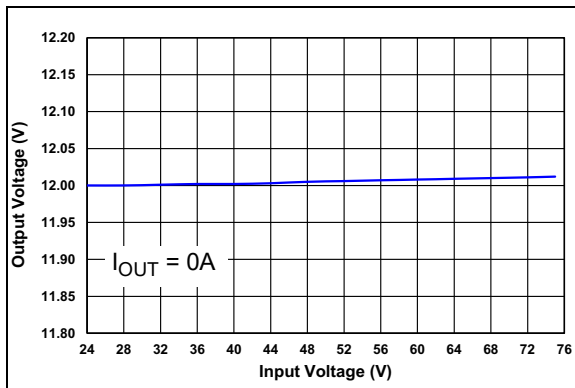
**Note:** Unless otherwise indicated,  $V_{IN} = 12V$ ;  $V_{OUT} = 5V$ ;  $f_{SW} = 500$  kHz/phase;  $V_{BST} - V_{SW} = 5V$ ;  $T_A = +25^\circ C$ .



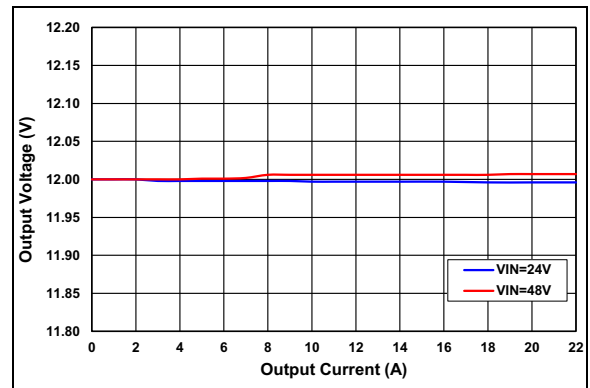
**FIGURE 2-7:** Line Regulation ( $V_{OUT} = 5V$ ).



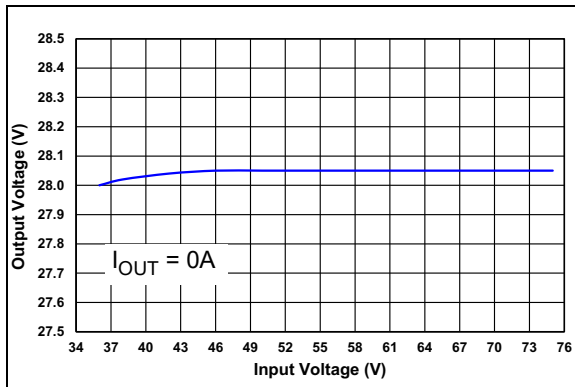
**FIGURE 2-10:** Load Regulation ( $V_{OUT} = 5V$ ).



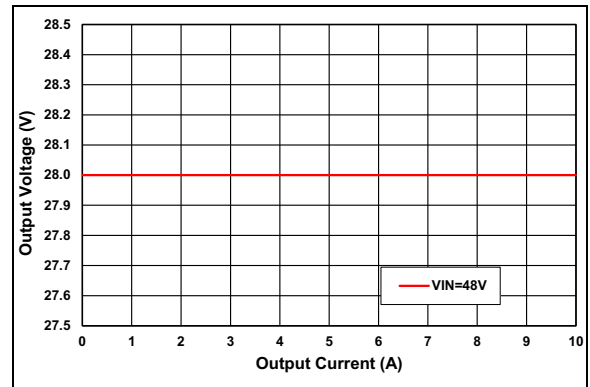
**FIGURE 2-8:** Line Regulation ( $V_{OUT} = 12V$ ).



**FIGURE 2-11:** Load Regulation ( $V_{OUT} = 12V$ ).



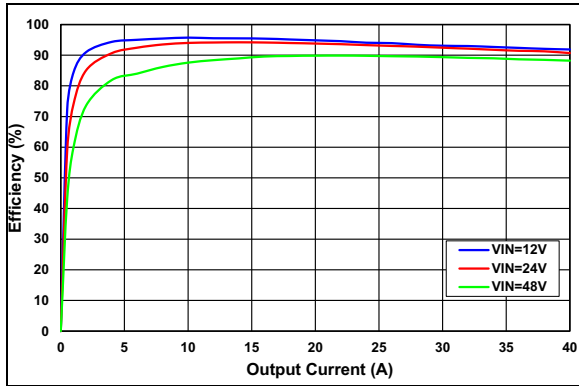
**FIGURE 2-9:** Line Regulation ( $V_{OUT} = 28V$ ).



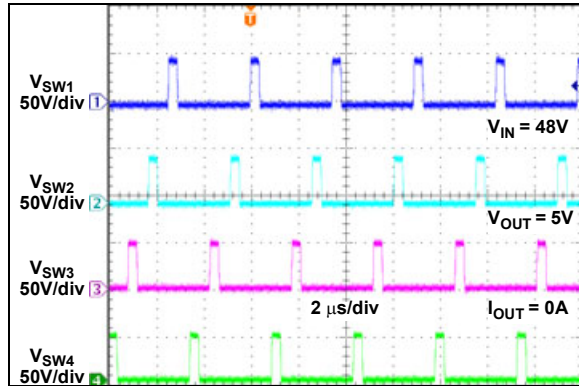
**FIGURE 2-12:** Load Regulation ( $V_{OUT} = 28V$ ).

# MIC2132

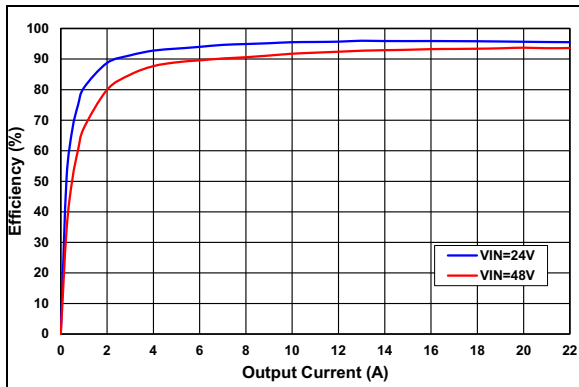
**Note:** Unless otherwise indicated,  $V_{IN} = 12V$ ;  $V_{OUT} = 5V$ ;  $f_{SW} = 500\text{ kHz/phase}$ ;  $L1 = L2 = L3 = L4 = 4.7\ \mu\text{H}$ ;  $R_{LIM} = 63.4\ \text{k}\Omega$ ; HS-FETs = N-ch 80V 30A 24 m $\Omega$ ; LS-FETs = N-ch 80V 46A 16 m $\Omega$ ;  $V_{BST} - V_{SW} = 5V$ ;  $T_A = +25^\circ\text{C}$ .



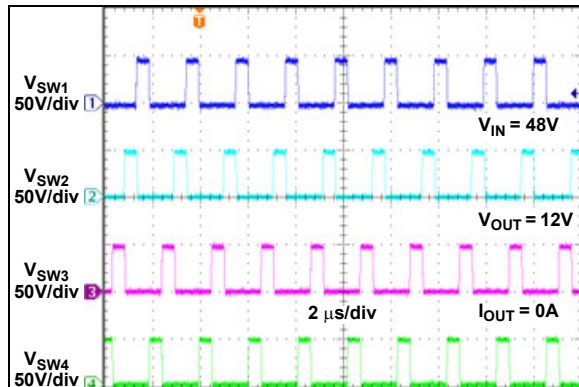
**FIGURE 2-13:** Efficiency vs. Output Current ( $V_{OUT} = 5V$ ).



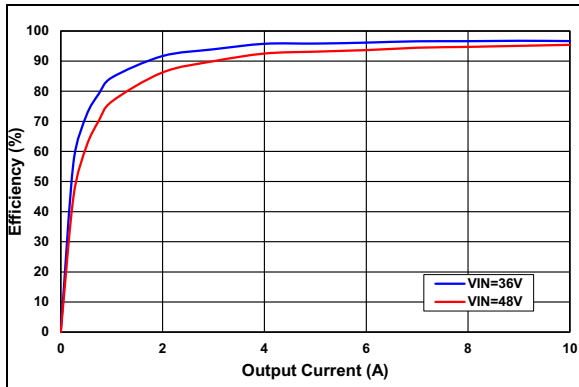
**FIGURE 2-16:** Switching Waveforms Phasing ( $V_{OUT} = 5V$ ,  $I_{OUT} = 0A$ ).



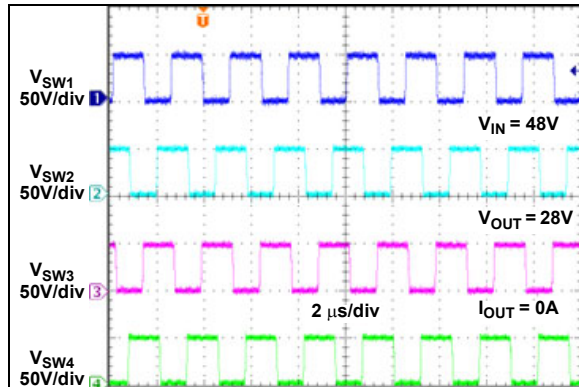
**FIGURE 2-14:** Efficiency vs. Output Current ( $V_{OUT} = 12V$ ).



**FIGURE 2-17:** Switching Waveforms Phasing ( $V_{OUT} = 12V$ ,  $I_{OUT} = 0A$ ).

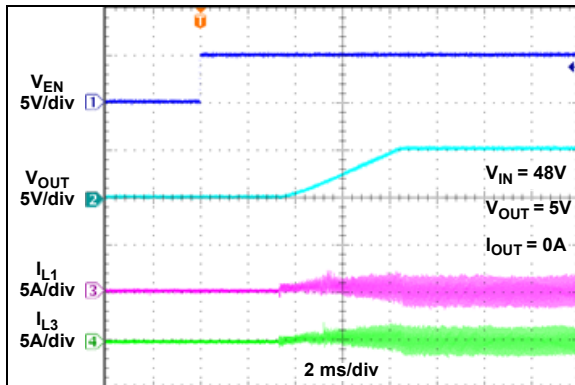


**FIGURE 2-15:** Efficiency vs. Output Current ( $V_{OUT} = 28V$ ).

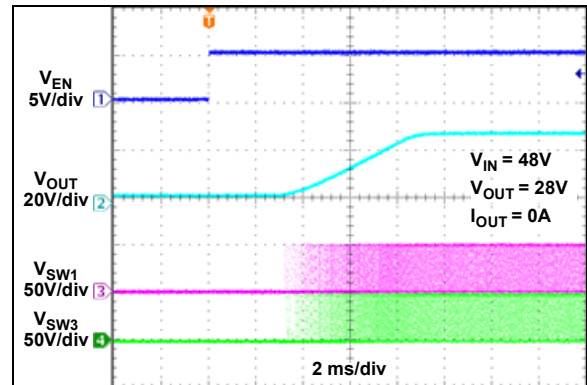


**FIGURE 2-18:** Switching Waveforms Phasing ( $V_{OUT} = 28V$ ,  $I_{OUT} = 0A$ ).

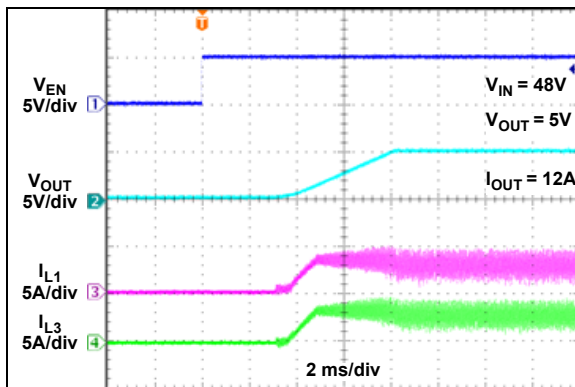
**Note:** Unless otherwise indicated,  $V_{IN} = 12V$ ;  $V_{OUT} = 5V$ ;  $f_{SW} = 500$  kHz/phase;  $L1 = L2 = L3 = L4 = 4.7$   $\mu$ H;  $R_{ILIM} = 63.4$  k $\Omega$ ; HS-FETs = N-ch 80V 30A 24 m $\Omega$ ; LS-FETs = N-ch 80V 46A 16 m $\Omega$ ;  $V_{BST} - V_{SW} = 5V$ ;  $T_A = +25^{\circ}C$ .



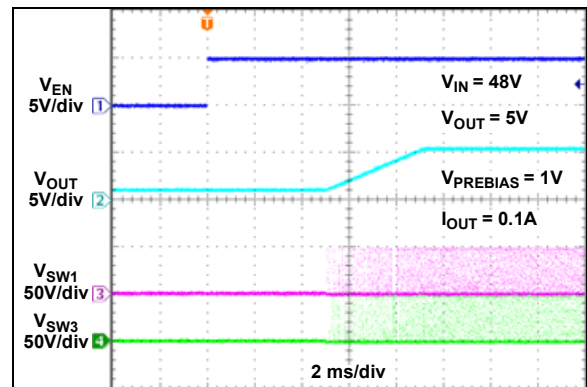
**FIGURE 2-19:** Soft Start with Enable ( $V_{OUT} = 5V$ ,  $I_{OUT} = 0A$ ).



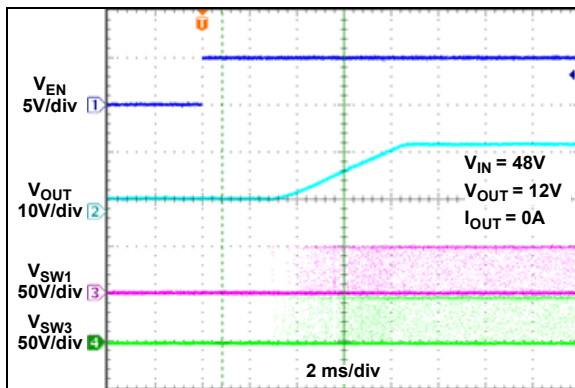
**FIGURE 2-22:** Soft Start with Enable ( $V_{OUT} = 28V$ ,  $I_{OUT} = 0A$ ).



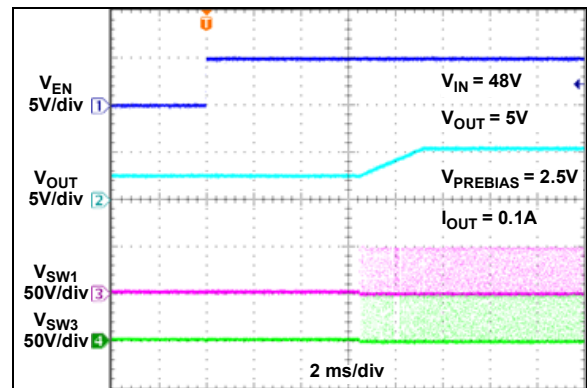
**FIGURE 2-20:** Soft Start with Enable ( $V_{OUT} = 5V$ ,  $I_{OUT} = 12A$ ).



**FIGURE 2-23:** Pre-Biased Start-up ( $V_{OUT} = 5V$ ,  $V_{PREBIAS} = 1V$ ).



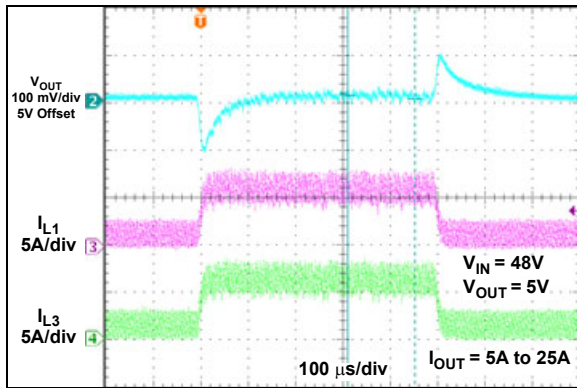
**FIGURE 2-21:** Soft Start with Enable ( $V_{OUT} = 12V$ ,  $I_{OUT} = 0A$ ).



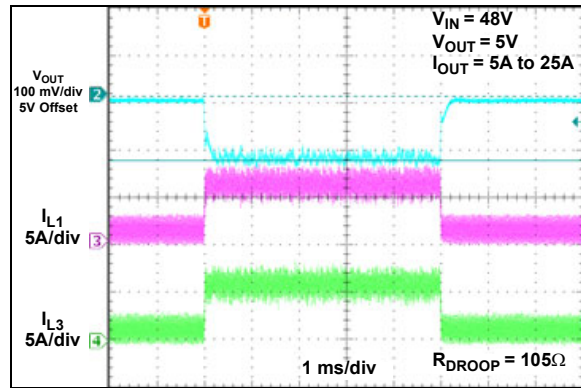
**FIGURE 2-24:** Pre-Biased Start-up ( $V_{OUT} = 5V$ ,  $V_{PREBIAS} = 2.5V$ ).

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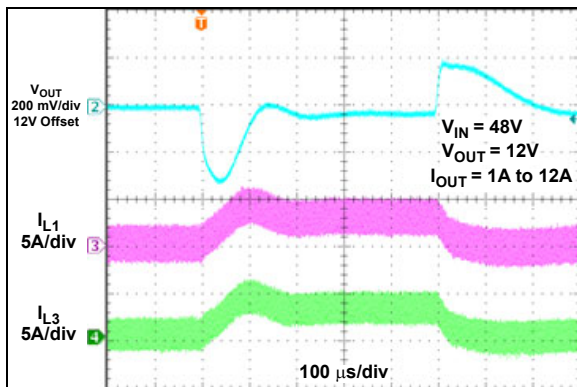
**Note:** Unless otherwise indicated,  $V_{IN} = 12V$ ;  $V_{OUT} = 5V$ ;  $f_{SW} = 500\text{ kHz/phase}$ ;  $L1 = L2 = L3 = L4 = 4.7\ \mu\text{H}$ ;  $R_{ILIM} = 63.4\ \text{k}\Omega$ ; HS-FETs = N-ch 80V 30A 24 m $\Omega$ ; LS-FETs = N-ch 80V 46A 16 m $\Omega$ ;  $V_{BST} - V_{SW} = 5V$ ;  $T_A = +25^\circ\text{C}$ .



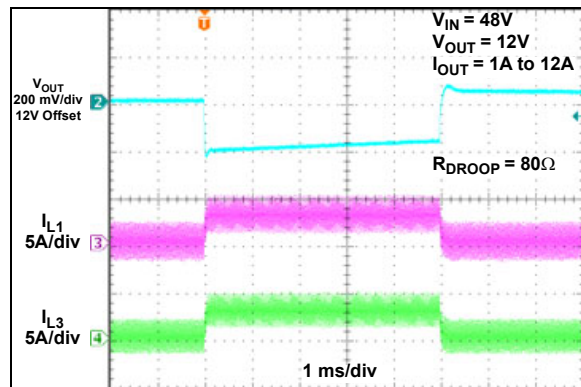
**FIGURE 2-25:** Load Transient without Droop ( $V_{OUT} = 5V$ ,  $I_{OUT} = 5A$  to  $25A$ ).



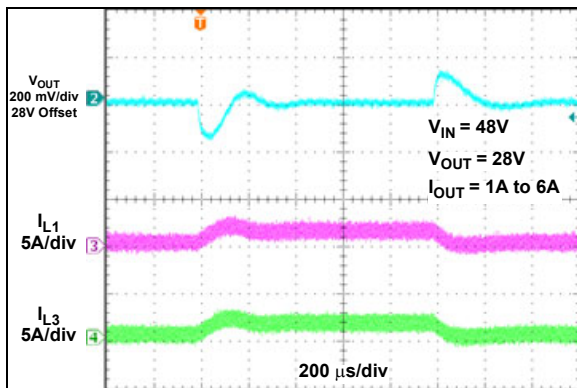
**FIGURE 2-28:** Load Transient with Droop ( $V_{OUT} = 5V$ ,  $I_{OUT} = 5A$  to  $25A$ ).



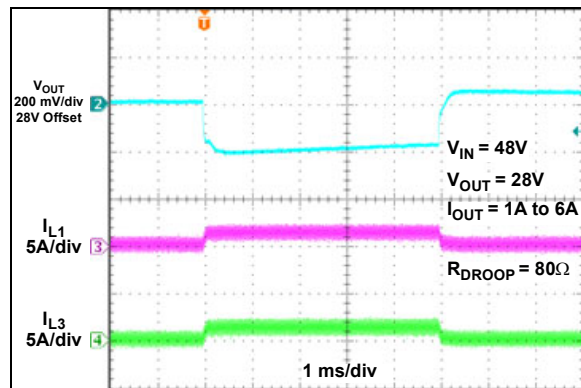
**FIGURE 2-26:** Load Transient without Droop ( $V_{OUT} = 12V$ ,  $I_{OUT} = 1A$  to  $12A$ ).



**FIGURE 2-29:** Load Transient with Droop ( $V_{OUT} = 12V$ ,  $I_{OUT} = 1A$  to  $12A$ ).



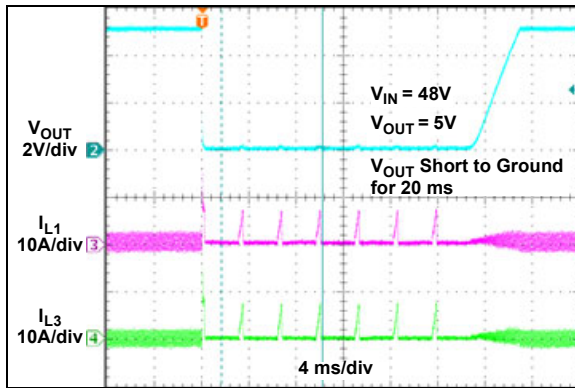
**FIGURE 2-27:** Load Transient without Droop ( $V_{OUT} = 28V$ ,  $I_{OUT} = 1A$  to  $6A$ ).



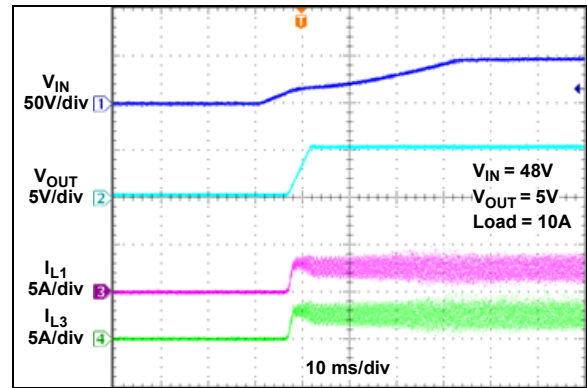
**FIGURE 2-30:** Load Transient with Droop ( $V_{OUT} = 28V$ ,  $I_{OUT} = 1A$  to  $6A$ ).



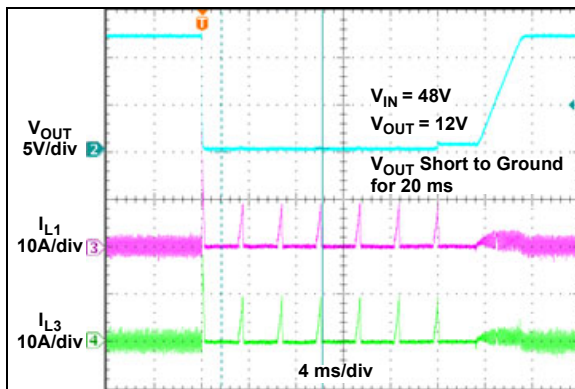
**Note:** Unless otherwise indicated,  $V_{IN} = 12V$ ;  $V_{OUT} = 5V$ ;  $f_{SW} = 500$  kHz/phase;  $L1 = L2 = L3 = L4 = 4.7$   $\mu$ H;  $R_{ILIM} = 63.4$  k $\Omega$ ; HS-FETs = N-ch 80V 30A 24 m $\Omega$ ; LS-FETs = N-ch 80V 46A 16 m $\Omega$ ;  $V_{BST} - V_{SW} = 5V$ ;  $T_A = +25^\circ C$ .



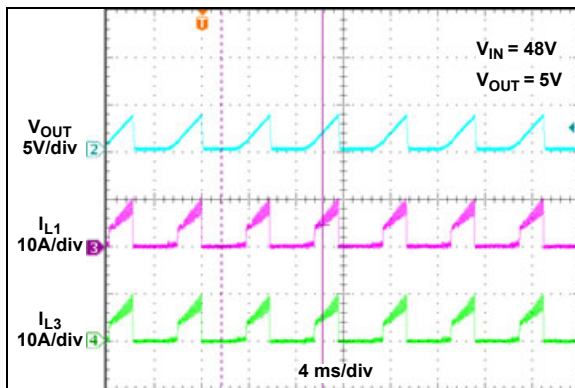
**FIGURE 2-31:** Output Short-Circuit Protection and Recovery ( $V_{OUT} = 5V$ ).



**FIGURE 2-34:**  $V_{IN}$  Power-up into 10A Load.



**FIGURE 2-32:** Output Short-Circuit Protection and Recovery ( $V_{OUT} = 12V$ ).



**FIGURE 2-33:** Current Limit per Phase.

# MIC2132

## 3.0 PIN DESCRIPTIONS

The descriptions of the pins are listed in [Table 3-1](#).

**TABLE 3-1: PIN FUNCTION TABLE**

Pin Number	Symbol	Description
1	CSN2	Current Sense Return pin for Phase 2. Connect Kelvin connection from the low-side FET source to CSN2 to avoid ground drops due to high current.
2	CSP2	Current Sense Positive pin for Phase 2. Connect Kelvin connection from the low-side FET drain to CSP2 to avoid ground drops due to high current.
3	CSN1	Current Sense Return pin for Phase 1. Connect Kelvin connection from the low-side FET source to CSN1 to avoid ground drops due to high current.
4	CSP1	Current Sense Positive pin for Phase 1. Connect Kelvin connection from the low-side FET drain to CSP1 to avoid ground drops due to high current.
5	ILIM	Current Limit Adjust Input pin. Connect a resistor from ILIM to AGND to set the current limit. Refer to <a href="#">Section 4.5.2 “Current Limit”</a> for more details. Both channels share the same current limit threshold. When connected in a stackable application, all ILIM pins are tied together, sharing common resistor sized for voltage drop, corresponding to current limit per phase.
6	CSH	Average Current Sense Voltage Output pin. Used for current sharing; see <a href="#">Section 4.5.1 “Current Balancing Between Phases”</a> and <a href="#">Section 4.5.9 “Adaptive Voltage Positioning (AVP), also Known as Droop Function (Recommended for CCM Only)”</a> . Connect 100 pF capacitor from CSH to AGND. In stackable application, tie all CSH pins together.
7	EN	Active-High Enable Input pin. 75V compatible with 1.2V precise threshold. Pull EN to GND to disable the buck converter output. Connect to VIN for always-on operation. EN can be used for power sequencing and as a UVLO adjustment input. For a precision UVLO, put an appropriately sized resistor divider from VIN to AGND and tie the midpoint to the EN pin.
8	VIN	Input Voltage to Controller pin. Connect to VIN through 1.21Ω resistor. Connect 1 μF capacitor from this pin to PGND.
9	VDD	5V LDO Output pin. Bias supply for the MIC2132 control logic circuit. Connect a minimum 2.2 μF low-ESR ceramic capacitor from VDD to AGND.
10	AGND	Analog Ground pin. Reference node for all the control logic circuits inside the MIC2132. Connect AGND to PGND at one point.
11	EXTVDD	Auxiliary LDO Input pin. Connect to a supply higher than 4.7V (typ) to bypass the internal high-voltage 5V LDO or leave unconnected/connected to ground when the EXTVDD pin is not used. Connect a 2.2 μF low-ESR ceramic capacitor between EXTVDD and AGND. EXTVDD can be connected to an external supply.
12	NPI	Next Phase Input pin. Connect APO of previous MIC2132 to NPI for multiphase operation.
13	APO	Active Phase Output pin. Connect APO to the next MIC2132 NPI pin for multiphase operation.
14	ONR	On-Time Request pin. It is an input or an output pin. Connect the ONR pins of all MIC2132 devices connected for multiphase operation. It is an output for the host and an input for the secondaries. The ONR output on the host has a pull-up capability of ~1 kΩ. When FBS is connected to VDD, it is an input (secondary).
15	OUTS	Output Voltage Sense pin. It is required to connect the OUTS pin to output through a 10 kΩ resistor and decouple to ground with a 100 nF capacitor directly for $V_{OUT} \leq 5V$ . For $V_{OUT} > 5V$ , it is required to connect the OUTS pin through a resistive divider from $V_{OUT}$ to AGND. The OUTS pin will set the correct frequency adaptive to the output voltage.
16	BST1	Phase 1 Bootstrap Capacitor Connection pin. The BST1 pin is the supply voltage input for the Phase 1 high-side MOSFET driver. Connect a 0.1 μF low-ESR ceramic capacitor between the BST1 pin and the SW1 pin.
17	DH1	Phase 1 High-Side Gate Driver Output pin. Connect DH1 to the Phase 1 high-side MOSFET gate.



**TABLE 3-1: PIN FUNCTION TABLE (CONTINUED)**

Pin Number	Symbol	Description
18	SW1	Phase 1 Switch Node Output pin. Connect one terminal of the Phase 1 inductor to the SW1 node.
19	DL1	Phase 1 Low-Side Gate Driver Output pin. Connect DL1 to the Phase 1 low-side MOSFET gate.
20	PGND	Power Ground pin. PGND is the return path for the low-side MOSFET current and for the low-side MOSFET driver. Connect all the PGND pins together and connect to the power ground plane.
21	PVDD	PVDD is Supply pin for the Low-Side MOSFET Driver. Connect to VDD through a 2.2Ω series resistor. Connect a minimum 4.7 μF low-ESR ceramic capacitor from PVDD to PGND.
22	DL2	Phase 2 Low-Side Gate Driver Output pin. Connect DL2 to the Phase 2 low-side MOSFET gate.
23	SW2	Phase 2 Switch Node Output pin. Connect one terminal of the Phase 2 inductor to the SW2 node.
24	DH2	Phase 2 High-Side Gate Driver Output Pin. Connect DH2 to the Phase 2 high-side MOSFET gate.
25	BST2	Phase 2 Bootstrap Capacitor Connection pin. The BST2 pin is the supply voltage input for the Phase 2 high-side MOSFET driver. Connect a 0.1 μF low-ESR ceramic capacitor between the BST2 pin and the SW2 pin.
26	PG	Open-Drain Power Good Output pin. PG is pulled to ground when the output voltage is below 80% of the target voltage. Pull-up to VDD through a 10 kΩ resistor to set logic high level when the output voltage is above 90% of the target voltage.
27	RIP_INJ	Ripple Injection Node pin. Connect series RC network from the RIP_INJ pin to FBS for injecting sufficient ripple for stable operation. Also connect a prepositioning resistor from this pin to AGND to set up the RIP_INJ pin voltage to its steady-state value. There is a 4.8 μA pull-up current when High-Z to preposition the common point of R <sub>INJ</sub> and C <sub>INJ</sub> .
28	FBS	Remote Feedback Input pin. Connect to the midpoint of a resistor divider from the output voltage to GFB to set the desired output voltage. Connect the FBS pin to VDD to configure MIC2132 as secondary in multiphase configuration.
29	GFB	Ground Feedback Remote Sense pin. Connect Kelvin sense directly across the output capacitor ground through the low-side FB resistor ground connection.
30	SS	Soft Start Adjustment pin. Connect a capacitor from the SS pin to AGND to adjust the soft start time. See more details in <a href="#">Section 4.5.5 “Soft Start”</a> . Connect an optional resistor across the SS pin to AGND for overshoot reduction during soft start.
31	FREQ	Frequency Programming Input pin. Connect to ground through a resistor set to the same switching frequency for each phase.
32	DROOP	Analog Output DROOP pin. This pin is for implementing the “Adaptive Voltage Positioning” feature. Connect a resistor from the DROOP pin to the feedback resistor divider. The DROOP voltage is proportional with inductor current for load currents greater than 0A.
—	EP	Exposed Pad pin. Connect it to AGND.

## 4.0 FUNCTIONAL DESCRIPTION

### 4.1 Control Architecture

The MIC2132 is an adaptive on-time, dual phase, synchronous step-down DC/DC controller. It is designed to operate over a wide 8V to 75V input voltage range and provides a regulated output voltage. An adaptive on-time control scheme is employed in order to obtain a constant switching frequency and simplify the control compensation.

The MIC2132 has a differential remote sense amplifier with unity gain for sensing output voltage. The differential remote sense amplifier helps regulate the output voltage at target level over the entire load range by avoiding parasitic voltage drops on the PCB. The output of the differential amplifier will be used as output voltage to the controller. The output voltage is sensed across the MIC2132 device's feedback remote sense FBS pin and ground feedback remote sense GFB pin via the voltage divider, and compared to a 0.6V Reference Voltage,  $V_{REF}$ , at a low-gain transconductance ( $g_m$ ) amplifier. The output of the  $g_m$  amplifier,  $V_{g_m}$ , is then further compared with another 1.2V reference,  $V_{REF\_COM}$ , at the error comparator. If the feedback voltage decreases and the output of the  $g_m$  amplifier is below 1.2V, then the error comparator will trigger the control logic and generate an on-time period. The on-time period length is predetermined by the  $T_{ON1}$  and  $T_{ON2}$  generation circuitries for Phase 1 and Phase 2, respectively.

#### EQUATION 4-1:

$$T_{ON(EST)} = \frac{V_{OUT}}{V_{IN} \times f_{SW}}$$

Where:

$V_{OUT}$  = Output Voltage

$V_{IN}$  = Power Stage Input Voltage

$f_{SW}$  = Switching Frequency of Each Phase

The internal logic starts maintaining the same switching frequency and phasing for each phase (180° for two phases; for stackable applications, 90° for four phases; 60° for six phases; 45° for eight phases).

Figure 4-1 shows the MIC2132 control loop timing during steady-state operation. During steady-state operation, the  $g_m$  amplifier senses the feedback voltage ripple, which is proportional to the output voltage ripple and the external ripple from the RIP\_INJ pin, injected to the FBS node at the turn-on instant of each phase. When the output of the  $g_m$  error amplifier falls below the reference voltage, an on-time period is triggered. The on-time of Phase 1 is determined by the  $T_{ON1}$  generator. The Phase 1  $T_{ON1}$  generator also includes current sharing error between phases. The Phase 1 high-side driver turns on the Phase 1 high-side FET during  $T_{ON1}$ . The Phase 1 high-side FET turn-off

instant depends on both the  $T_{ON}$  estimation and current sharing error. At the end of Phase 1  $T_{ON1}$ , the internal high-side driver turns off the Phase 1 high-side FET and the low-side driver turns on the Phase 1 low-side FET. The Phase 1 off-time period length depends upon the feedback voltage error in the next cycle for Phase 1. When the output of the  $g_m$  error amplifier falls below the reference voltage in the second cycle, the Phase 2 on-time period is triggered. The on-time of Phase 2 is determined by the  $T_{ON2}$  generator. The Phase 2  $T_{ON2}$  generator also includes current sharing error between phases. The Phase 2 high-side driver turns on the Phase 2 high-side FET during  $T_{ON2}$ . The high-side FET turn-off instant depends on both the  $T_{ON}$  estimation and current sharing error. At the end of Phase 2  $T_{ON2}$ , the internal high-side driver turns off the Phase 2 high-side FET and the low-side driver turns on the Phase 2 low-side FET. The duration of the Phase 2 off-time period depends upon the feedback voltage error in the next Phase 2 cycle. The above cycles repeat in a daisy-chain ring, and both phases support the load current alternately and maintain output voltage. In steady-state operation,  $T_{ON1} = T_{ON2}$ ,  $T_{OFF1} = T_{OFF2}$  and this way, the resulting phase difference is 180 degrees. For a stackable configuration of four phases in a similar way,  $T_{ON1} = T_{ON2} = T_{ON3} = T_{ON4}$  and  $T_{OFF1} = T_{OFF2} = T_{OFF3} = T_{OFF4}$  generates a 90-degree phasing.

If the off-time period determined by the feedback voltage is less than the Minimum Off-Time,  $T_{OFF(MIN)}$ , which is about 360 ns, then the MIC2132 control logic will apply the  $T_{OFF(MIN)}$  instead to either phase. The minimum  $T_{OFF(MIN)}$  period is required to maintain enough energy in the Boost Capacitor ( $C_{BST}$ ) to drive the high-side MOSFET.

The maximum duty cycle is obtained from the 360 ns  $T_{OFF(MIN)}$ :

#### EQUATION 4-2:

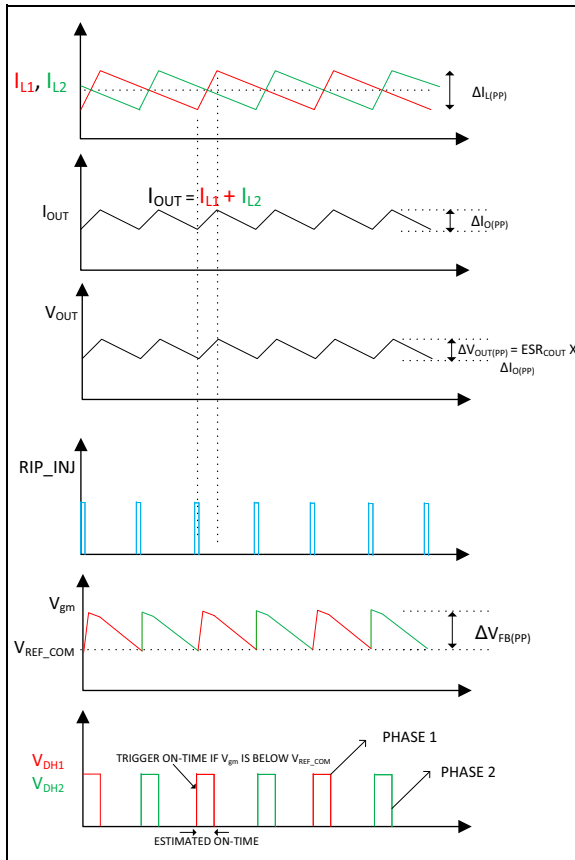
$$D_{MAX} = \frac{T_S - T_{OFF(MIN)}}{T_S} = 1 - \frac{360 \text{ ns}}{T_S}$$

Where:

$$T_S = 1/f_{SW}$$

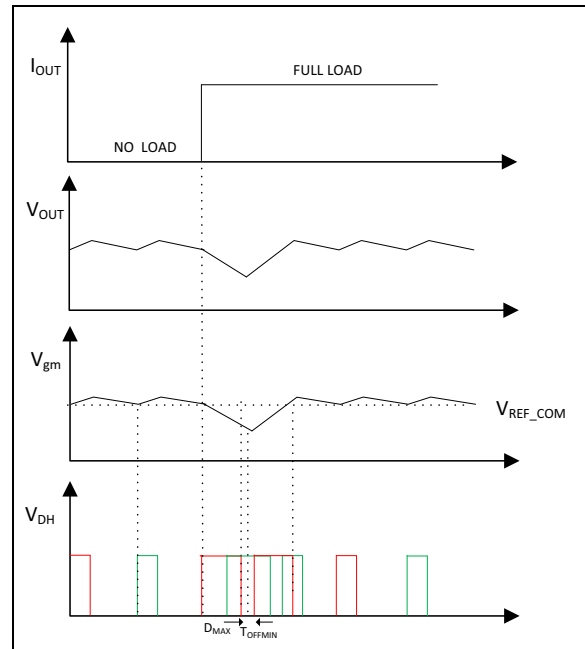
It is not recommended to use the MIC2132 with an off-time close to  $T_{OFF(MIN)}$  during steady-state operation. Equation 4-2 should be used to choose the  $T_S$  for a lower switching frequency when the  $D_{MAX}$  is reached, if  $V_{IN}$  is very close to  $V_{OUT}$ , knowing that the buck converter duty cycle equals  $V_{OUT}$  divided by  $V_{IN}$ .

The actual on-time and the resulting switching frequency will vary with the part-to-part variation in the rise and fall times of the external MOSFETs, the output load current and the variations in the  $V_{DD}$  voltage. Also, the minimum  $T_{ON}$  results in a lower switching frequency in high  $V_{IN}$  to  $V_{OUT}$  applications, such as 28V to 1.0V.

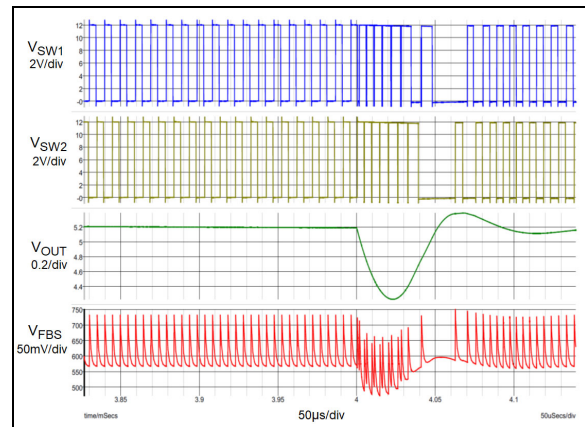


**FIGURE 4-1:** Steady-State Operation (FB Ripple Shows Injected and ESR Ripple Only, Reactive Impedances Neglected).

Figure 4-2 shows the operation of the MIC2132 during load transient. The output voltage drops due to the sudden load increase, which causes the  $V_{FBS}$  to decrease and the output voltage of the  $g_m$  amplifier,  $V_{gm}$ , to be less than  $V_{REF\_COM}$ . This will cause the error comparator to trigger an on-time period. At the end of the on-time period, a Minimum Off-Time,  $T_{OFF(MIN)}$ , is generated to charge  $C_{BST}$ , since the feedback voltage is still below  $V_{REF}$ . Then, the next on-time period is triggered and applies  $D_{MAX}$  due to the low feedback voltage. Therefore, the switching frequency changes during the load transient to deliver  $D_{MAX}$  and zero duty cycle when the high-current load disappears for both phases, but returns to the nominal fixed frequency once the output has stabilized at the new load current level. With the varying duty cycle and switching frequency, the output recovery time is fast and the output voltage deviation is small in the MIC2132 converter. The phases will overlap during load transient until the output voltage error is corrected. The transient response is shown in Figure 4-3.



**FIGURE 4-2:** MIC2132 Load Transient Response Timing.

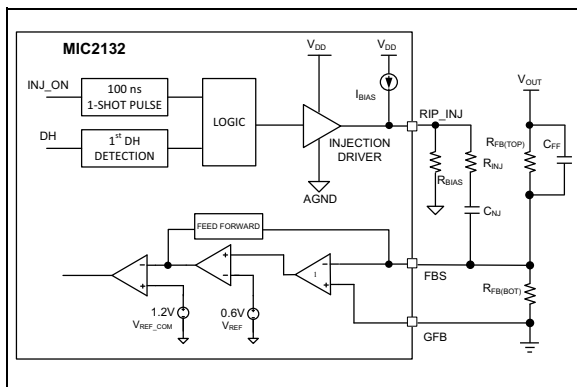


**FIGURE 4-3:** MIC2132 Load Transient Response.

Unlike true Current-mode control, the MIC2132 uses the output voltage ripple to trigger an on-time period. The output voltage ripple is proportional to the inductor current ripple if the ESR of the output capacitor is large enough. In order to meet the stability requirements, the MIC2132 feedback voltage ripple must be in phase with the inductor current ripple, and large enough to be sensed by the  $g_m$  amplifier and the error comparator. The recommended feedback voltage ripple is 20 mV to 100 mV. If a low-ESR output capacitor is selected, then the feedback voltage ripple may be too small to be sensed by the  $g_m$  amplifier and the error comparator. Also, the output voltage ripple and the feedback voltage ripple are not necessarily in phase with the inductor current ripple if the ESR of the output capacitor is very low. In these cases, ripple injection is required to ensure proper operation.

## 4.2 Start-up Into Pre-Bias Load

To get proper pre-bias start-up performance, the voltage at the junction of  $C_{INJ}$  and  $R_{INJ}$  needs to be at its steady-state value when the device starts switching. This is done by biasing the RIP\_INJ pin voltage using a current source ( $I_{BIAS}$ ) at the RIP\_INJ pin and a resistor ( $R_{BIAS}$ ) at the RIP\_INJ pin before the device starts switching. The Injection (INJ) driver will be in High-Impedance mode before the device starts switching. This results in a voltage equal to  $I_{BIAS} \times R_{BIAS}$  at the RIP\_INJ pin before switching starts. This voltage charges the  $C_{INJ}$  cap to the value of  $I_{BIAS} \times R_{BIAS}$ . As the  $C_{INJ}$  takes time to charge to the final voltage, depending on the  $C_{INJ} \times (R_{INJ} + R_{FB(BOT)})$ , the  $I_{BIAS}$  must be enabled before the switching starts. The MIC2132 has a POK delay of  $\approx 4$  ms (i.e., when EN is high, the device starts switching after  $\approx 4$  ms). Therefore, this 4 ms delay is enough to charge  $C_{INJ}$  to the final value. Once the device starts switching, the  $I_{BIAS}$  will no longer have any effect, as the ripple injection driver will be either high or low (the ripple injection driver will not be in High-Impedance mode when the device starts switching).



**FIGURE 4-4:** Circuit to Obtain Proper Pre-Bias Start-up Performance and Ripple Injection.

$I_{BIAS}$  is an internal current source.  $R_{BIAS}$  is an external resistor from RIP\_INJ to AGND.  $R_{BIAS}$  can be calculated using the formula below:

### EQUATION 4-3:

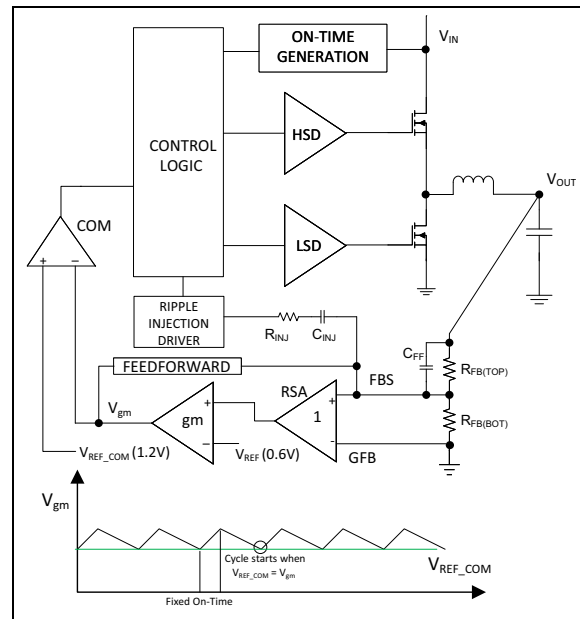
$$R_{BIAS} = \frac{5V \times 100 \text{ ns} \times f_{SW}}{I_{BIAS}}$$

Where:  
 $5V \times 100 \text{ ns} \times f_{SW}$  = Average Voltage on the RIP\_INJ Pin

Note that as  $R_{BIAS}$  is always present, it draws an additional current from the INJ driver when the RIP\_INJ pin is 5V for 100 ns. This adds to the device's  $I_Q$ . However, its contribution to the device's  $I_Q$  will be low because this current will be present for 100 ns only. Another thing to note is that the INJ driver must be capable of supplying this additional current.

## 4.3 Stability Analysis

The MIC2132 uses ripple-based constant on-time architecture to generate switching pulses. The magnitude of the ripple needs to be in the range of 20 mV to 100 mV. In order to avoid ripple voltage variation with input voltage, ripple voltage is injected from the third node through the RIP\_INJ pin. Figure 4-5 shows the ripple injection at the FBS node with respect to the reference voltage.



**FIGURE 4-5:** MIC2132 Ripple Injection at FBS Node.

The output capacitors generally have three components. The capacitive ripple lags the inductor current ripple. The ESR ripple is in phase with the inductor current. The ESL ripple effect is minimal in low-voltage capacitors.

## 4.4 Ripple Injection Circuit Components Selection

Follow the steps below for selecting the ripple injection circuit components if low-ESR output capacitors are used. The below procedures provide a good starting point for selecting the ripple injection components. Final values should be confirmed by laboratory measurements.

1. Calculate the product of  $R_{INJ}$  and  $C_{FF}$  for a given injected Feedback Ripple Voltage,  $\Delta V_{FB}$ , using the equation below. Choose  $\Delta V_{FB}$  in the range of 40 mV to 500 mV. A good starting point for  $\Delta V_{FB}$  is 50 mV.

### EQUATION 4-4:

$$R_{INJ} \times C_{FF} = \frac{5V \times 100 \text{ ns}}{\Delta V_{FB}}$$

Where:

$\Delta V_{FB}$  = Injected Feedback Ripple Voltage

2. Choose  $C_{FF}$  in the range from 0.47 nF to 10 nF.
3. Calculate  $R_{INJ}$  using the above equation.
4. Calculate the Top Feedback Resistor,  $R_{FB(TOP)}$ , value using the equation below.

### EQUATION 4-5:

$$R_{FB(TOP)} \geq \frac{1}{2 \times \pi \times C_{FF} \times 0.8 \times f_{LC}}$$

Where:

$f_{LC}$  = LC Resonant Frequency =  $1/(2 \times \pi \times \text{sqrt}(L \times C_{OUT}))$

5. Calculate the Bottom Feedback Resistor,  $R_{FB(BOT)}$ , value using the equation below:

### EQUATION 4-6:

$$R_{FB(BOT)} = \frac{R_{FB(TOP)}}{\left[ \frac{V_{OUT}}{V_{REF}} - 1 \right]}$$

Where:

$V_{OUT}$  = Target Output Voltage

$V_{REF}$  = Reference Voltage = 0.6V for MIC2132

6. Estimate the crossover frequency using [Equation 4-7](#). If  $f_{CO(EST)}$  is above  $f_{SW}/5$ , lower the  $C_{FF}$  value and repeat procedure 6.

### EQUATION 4-7:

$$f_{CO(EST)} = \frac{R_{INJ} \times C_{FF}}{\pi \times L \times C_{OUT}} \times \frac{V_{OUT} \times 10^6}{f_{SW}}$$

Where:

$L$  = Inductance

$C_{OUT}$  = Output Capacitance

$V_{OUT}$  = Output Voltage

$f_{SW}$  = Switching Frequency

- 7a) Select  $C_{INJ}$  using the below equation if  $f_{CO(EST)}$  calculated above meets [Equation 5-11](#).

### EQUATION 4-8:

$$C_{INJ} \geq \frac{1}{0.8 \times R_{INJ} \times f_{CO(EST)}}$$

Add a resistor in parallel with the soft start capacitor connected to the SS pin if  $C_{INJ} > C_{FF} \times (R_{FB(TOP)} R_{FB(BOT)})$ . This ensures that there is no overshoot at the end of the soft start. Use [Equation 4-9](#) to select the parallel resistor value.

### EQUATION 4-9:

$$R_{SS} \geq \frac{0.8V}{I_{SS}}$$

Where:

$I_{SS}$  = Soft Start Current Source = 1.2  $\mu$ A

- 7b) Select  $C_{INJ}$  using the below guidelines if  $f_{CO(EST)}$  is low (typically below  $f_{SW}/15$ ). Calculate the maximum Equivalent Series Resistance (ESR) of the output capacitor using [Equation 4-10](#).

### EQUATION 4-10:

$$ESR_{COUT} \leq \frac{\Delta V_{OUT\_TRANS}}{\Delta I_{LOAD\_STEP}}$$

Where:

$\Delta I_{LOAD\_STEP}$  = Magnitude of the Load Transient

$\Delta V_{OUT\_TRANS}$  = Acceptable Output Voltage Deviation during Load Transient

Calculate the output capacitance using [Equation 4-11](#).

### EQUATION 4-11:

$$C_{OUT} \geq \frac{1}{\pi \times f_{CO} \times ESR_{COUT}}$$

Calculate  $C_{INJ}$  using [Equation 4-12](#).

### EQUATION 4-12:

$$C_{INJ} = C_{FF} \times \frac{ESR_{COUT}}{2 \times \pi \times f_{CO} \times L} \times \frac{V_{OUT}}{5V \times 100 \text{ ns} \times f_{SW}}$$

Using too low a  $C_{INJ}$  may result in oscillations at the beginning of the soft start. These oscillations can be reduced either by using a higher  $C_{INJ}$  or  $C_{OUT}$ , by reducing the feedback ripple.

# MIC2132

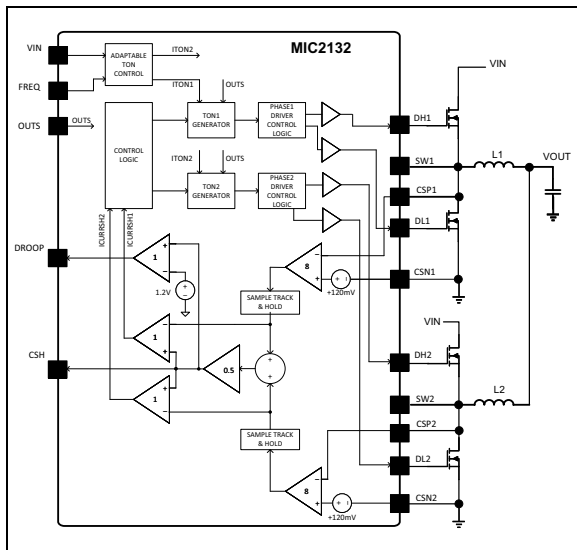
## 4.5 Detailed Device Description

The MIC2132 always operates in CCM and both phases support the load current equally at high loads.

### 4.5.1 CURRENT BALANCING BETWEEN PHASES

One important benefit of the two-phase operation is the thermal advantage gained by distributing the heat over multiple devices and a greater PCB area. By doing this, the system designer avoids the complexity of driving parallel MOSFETs and the expense of using expensive heatsinks.

In order to achieve the thermal advantage, it is important that each phase carries the same amount of current at any load level. In the MIC2132, both phase currents are sensed across the low-side MOSFET,  $R_{DS(ON)}$ , during off-time. The low-side MOSFET current is tracked during off-time and held close to peak value in the valley point. The average current information is generated by summing all the phases' sensed currents and dividing by the number of phases (two for two phases). An error current per phase is generated by making the difference between the average current information and each phase current, which is used to modulate  $T_{ON1}$  and  $T_{ON2}$  in order to cancel the error in the current sharing.

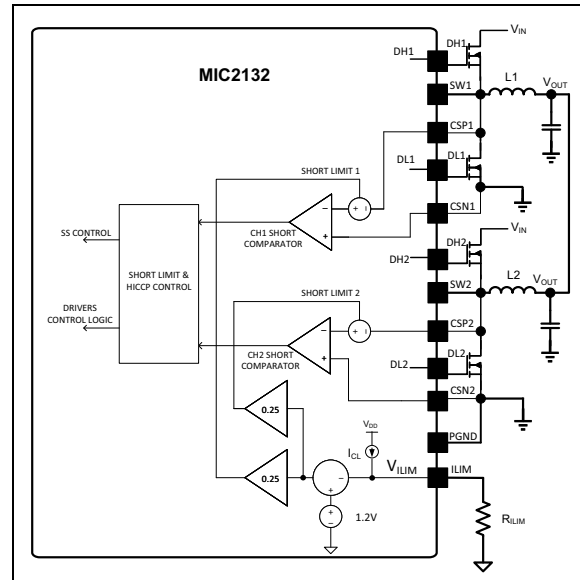


**FIGURE 4-6:** MIC2132 Current Sharing Circuit.

### 4.5.2 CURRENT LIMIT

The MIC2132 uses the  $R_{DS(ON)}$  of the external low-side power MOSFET to sense overcurrent conditions, or a sense resistor inserted with the source of the bottom FET can be used for more accurate results and not requiring temperature compensation. The bottom FET  $R_{DS(ON)}$  sensing method will avoid adding cost, use of additional board space and power losses taken by a discrete current sense resistor.

The current limit threshold can be programmed by connecting a resistance from the ILIM pin to AGND. Both phases use the same current limit threshold.



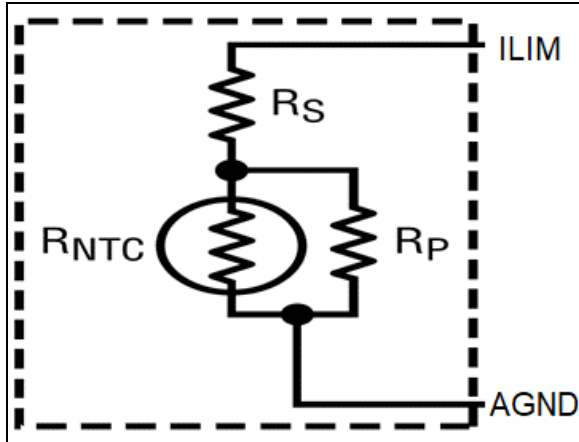
**FIGURE 4-7:** MIC2132 Current-Limiting Circuit.

The MIC2132 forces a constant 9.6  $\mu\text{A}$  current through the ILIM setting resistor, tied from the ILIM pin to AGND, to program  $V_{ILIM}$ .

In each switching cycle of both phases of the MIC2132 converter, the inductor valley current is sensed by monitoring the  $V_{DS}$  voltage across the low-side MOSFET during the off period. There is a 150 ns (typical) blanking period before each current sense signal is considered for protection. The blanking period improves noise immunity. If the valley low-side MOSFET current is greater than the current limit threshold current for seven consecutive cycles in either phase, then the MIC2132 turns off the high-side and low-side MOSFETs of both phases and a soft start sequence is triggered after the hiccup timer has expired. This mode of operation is called Hiccup mode and its purpose is to protect the downstream load in case of a hard short. Figure 4-8 illustrates the MIC2132 operation during overload conditions. When the load current is increased gradually, the inductor current also increases, as shown in Figure 4-8. When the load current is around the current limit threshold, the high-side and low-side MOSFET current can be higher than the current limit, as highlighted in Figure 4-8 as Case #1. In Case #1, even though the low-side MOSFET instantaneous current exceeds the current limit threshold for some duration, the low-side MOSFET current is lower than the current limit at the end of the 150 ns blanking time. This causes the MIC2132 to not enter the current limit protection and initiate the next high-side MOSFET turn-on cycle. After the high-side MOSFET is turned on, the current ramps up to a value that is determined by the operating duty cycle and inductor value. When the high-side MOSFET is turned off and







**FIGURE 4-9:** Resistance Network Used with  $R_{NTC}$  Resistor for Linearization and Fitting the Temperature Coefficient of MOSFET  $R_{DS(on)}$ .

In case a temperature-independent resistor sensing is used, a simple temperature constant standard resistance is used on the ILIM pin.

#### 4.5.3 NEGATIVE CURRENT LIMIT

The MIC2132 supports a cycle-by-cycle negative current limit. The absolute value of the negative current-limiting threshold is 50% of the programmed current limit. If the negative low-side MOSFET current is going to trigger a negative current limit, the low-side MOSFET will be turned off and allow current through its body diode. During this time, the output voltage tends to rise, because this protection limits the current to discharge the output capacitor. In order to prevent a huge reverse current over the short limit value, the low-side FET turns on after 500 ns, maintaining negative current at the programmed level.

#### 4.5.4 PRECISION ENABLE (EN)

The precision Enable (EN) input is used to control the regulator. The precision feature allows the simple sequencing of multiple power supplies with a resistor divider from another supply. Connecting this pin to ground, or to a voltage lower than 1.2V (typical), will turn off the regulator. In this state, the current drain from the input supply is 25  $\mu$ A (typical) at a 12V input voltage.

The EN input has an internal pull-up of about 6  $\mu$ A. Therefore, this pin can be left floating or pulled to a voltage greater than 1.2V (typical) to turn the regulator on. The hysteresis on this input is about 65 mV (typical) below the 1.2V (typical) threshold. When driving the enable input, the voltage must never exceed the absolute maximum specification for this pin. Although an internal pull-up is provided on the EN pin, it is a good practice to pull the input high when this feature is not used, especially in noisy environments. This can be done easily by connecting a high-value resistor (1 M $\Omega$ ) between the VIN and EN pins. The MIC2132 device also incorporates an internal input Undervoltage Lock-

out (UVLO) feature. This prevents the regulator from turning on when the input voltage is not high enough to properly bias the internal circuitry. The rising threshold is 4.3V (typical) while the falling threshold is 3.9V (typical). In some cases, these thresholds may be too low to provide good system performance. The solution is to use the EN input as an external programmable input UVLO to disable the part when the input voltage falls below a target lower threshold. This is often used to prevent excessive battery discharge or early turn-on during start-up. This method is also recommended to prevent abnormal device operation in applications where the input voltage falls below the minimum of 4.5V. Figure 4-10 shows the connections to implement this method of UVLO. Equation 4-17 and Equation 4-18 can be used to determine the correct resistor values.

#### EQUATION 4-17:

$$R_{TOP} = R_{BOT} \times \left( \frac{V_{OFF}}{V_{ENTH} - V_{ENHYS}} - 1 \right)$$

Where:

- $R_{TOP}$  = Top Resistor of the  $V_{IN}$  Voltage Resistor Divider
- $R_{BOT}$  = Bottom Resistor of the  $V_{IN}$  Voltage Resistor Divider
- $V_{OFF}$  = Target  $V_{IN}$  Voltage Below which the Regulator Turns Off
- $V_{ENTH}$  = Device Enable Upper Threshold Voltage
- $V_{ENHYS}$  = Enable Threshold Hysteresis

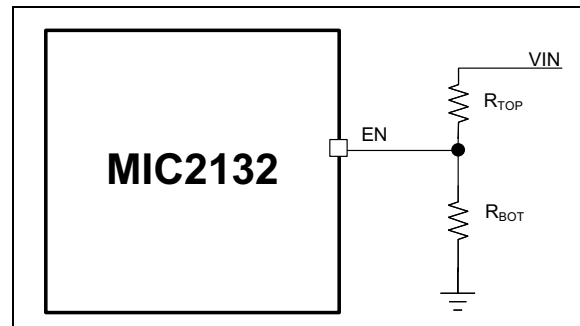
#### EQUATION 4-18:

$$V_{ON} = V_{OFF} \times \left( \frac{V_{ENTH}}{V_{ENTH} - V_{ENHYS}} \right)$$

Where:

- $V_{OFF}$  = Input Voltage where the Regulator Shuts Off
- $V_{ON}$  = Input Voltage where the Regulator Turns On
- $V_{ENHYS}$  = Enable Threshold Hysteresis
- $V_{ENTH}$  = Enable Upper Threshold Voltage

Due to the 6  $\mu$ A pull-up, the current in the divider must be much higher than this. A value of 20 k $\Omega$  for  $R_{BOT}$  is a good first choice.



**FIGURE 4-10:** External Programmable  $V_{IN}$  UVLO Connections.



## 4.5.5 SOFT START

Soft start reduces the power supply input surge current at start-up by controlling the output voltage rise time. The input surge appears while the output capacitor is charged up. A slower output rise time will draw a lower input surge current.

The MIC2132 features adjustable soft start time. The soft start time can be adjusted by changing the value of the capacitor connected from the SS pin to AGND. The soft start time can be adjusted from 5 ms to 100 ms. The MIC2132 forces 1.2  $\mu\text{A}$  current from the SS pin. This constant current flows through the soft start capacitor connected from the SS pin to AGND in order to adjust the soft start time.

The soft start capacitor value for the desired  $V_{\text{OUT}}$  ramp-up time can be calculated from [Equation 4-19](#).

### EQUATION 4-19:

$$C_{SS} = \frac{1.2 \mu\text{A} \times t_{SS}}{V_{REF}}$$

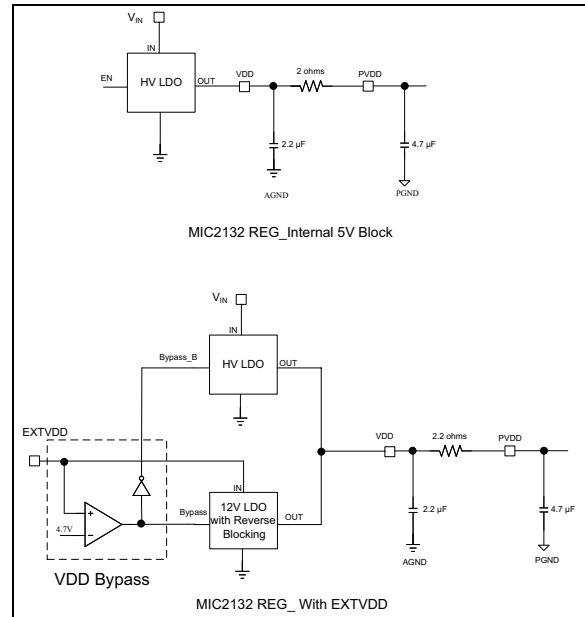
Where:

$t_{SS}$  = Output Voltage Soft Start Ramp-up Time

## 4.5.6 VDD REGULATOR AND EXTVDD LDO

The MIC2132 has an integrated high-voltage LDO that provides a 5V regulated output from Input Voltage,  $V_{\text{IN}}$ , ranging from 8V to 75V. When  $V_{\text{IN}} < 5.5\text{V}$ ,  $V_{\text{DD}}$  must be tied to the  $V_{\text{IN}}$  pins to bypass the internal linear regulator. The internal LDO powers the control circuitry from the VDD pin and gate drive current from the PVDD pin.

The MIC2132 also features an auxiliary low-voltage LDO, which is powered by EXTVDD. When the voltage on the EXTVDD is at 4.7V (typical) or higher, this auxiliary LDO is enabled and powers all the internal circuitry. At the same time, the main high-voltage LDO is disabled. This increases the efficiency of the system by reducing the differential voltage across the high-voltage LDO, hence reducing the power losses in the LDO. In general, the output of the buck converter is used as the power supply for the auxiliary LDO by connecting the EXTVDD pin to the output of the buck converter. The maximum voltage that can be applied at EXTVDD is limited to 14V. [Figure 4-11](#) shows the internal 5V LDO and EXTVDD connection in the MIC2132.



**FIGURE 4-11: MIC2132 EXTVDD.**

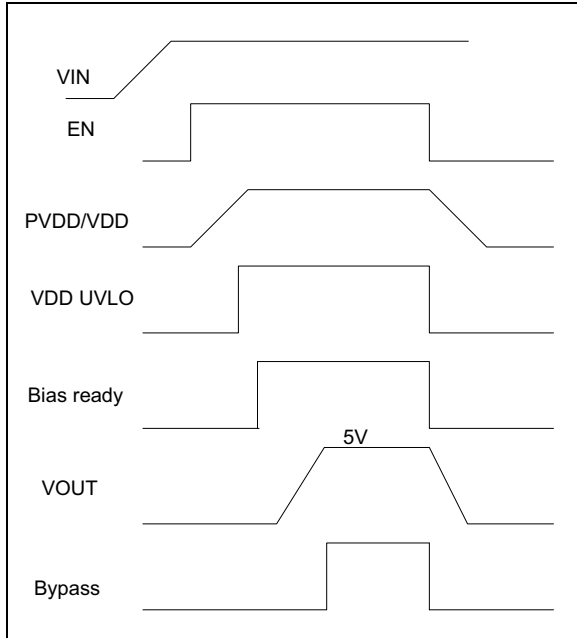
Given that the EXTVDD is powered from the  $V_{\text{OUT}}$  of the buck regulator, the  $V_{\text{OUT}}$  is noisy if there is a fast changing load. When  $V_{\text{OUT}} > 5\text{V} + V_{\text{DROPOUT}}$ , the noise could be suppressed by a loop of 12V LDO. However, when  $V_{\text{OUT}} = 5\text{V}$ , the 12V LDO works in Dropout mode and there is no loop gain. The LDO acts just like a resistor. It is not recommended to connect EXTVDD to  $V_{\text{OUT}}$  if  $V_{\text{OUT}} < 5\text{V}$ .

## 4.5.7 POWER GOOD (PG)

The Power Good (PG) pin is an open-drain output, which indicates logic high when the output is nominally over 88% of its steady-state voltage. A pull-up resistor of more than 10 k $\Omega$  should be connected from PG to VDD. During soft start, the PG is held low and is allowed to be pulled high after  $V_{\text{OUT}}$  is achieved over 88% of the target level.

## 4.5.8 SEQUENCING

The MIC2132 has a precision enable function. The EN pin threshold will either enable/disable switching. When the EN pin voltage is higher than 1.2V (typical), the MIC2132 is put into operation. The internal regulator will power up and start switching. [Figure 4-12](#) shows the EN pin sequencing.



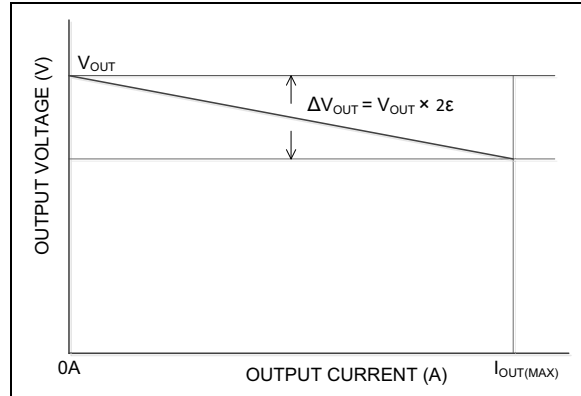
**FIGURE 4-12:** EN Pin Sequencing.

When the EN pin voltage is below the lower EN threshold, the MIC2132 goes into Shutdown mode. When in Shutdown mode, the MIC2132 stops switching and all internal control circuitry switches off to reduce the quiescent current. The EN pin, along with the PG pin, can be used for sequencing multiple MIC2132 devices. It is recommended to power up VIN before the EN signal.

#### 4.5.9 ADAPTIVE VOLTAGE POSITIONING (AVP), ALSO KNOWN AS DROOP FUNCTION (RECOMMENDED FOR CCM ONLY)

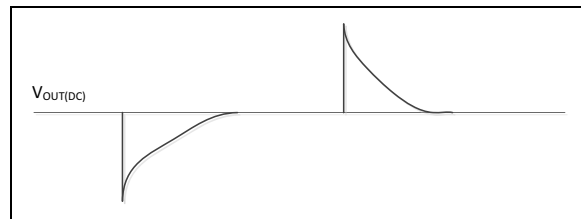
In some high-current applications, a requirement on a precisely controlled output impedance is imposed. This dependence of output voltage on load current is often termed, “droop”, “load line” regulation, or Adaptive Voltage Positioning (AVP).

The basic functionality of the AVP function is to achieve a controlled output resistance for the buck regulator, so that at 0A load, the output is + $\epsilon\%$  higher than the nominal voltage and at maximum load, the output is - $\epsilon\%$  related to the nominal output value, as shown in Figure 4-13.

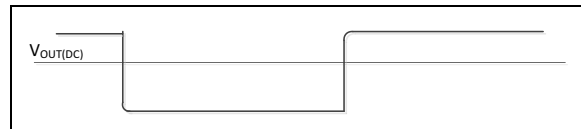


**FIGURE 4-13:** AVP Ideal Output Resistive Characteristic.

It is necessary to achieve the resistive characteristic above over the full frequency range of output loads.



**FIGURE 4-14:**  $V_{OUT}$  Load Transient Error without AVP/DROOP.



**FIGURE 4-15:**  $V_{OUT}$  Load Transient Error with AVP/DROOP.

Figure 4-14 and Figure 4-15 explain how the AVP design window of  $\pm\epsilon$  can be used to reduce the amount of the output capacitor necessary to sustain the load transient. Alternatively, the AVP can be used to improve the error of the load transient if it is decided to keep the same output capacitor.

The DROOP pin is an analog output, which provides a voltage proportional with the output current in CCM, according to the formula in Equation 4-20.

#### EQUATION 4-20:

$$V_{DROOP} = V_{CSH} - 1.2V = 8 \times R_{SENSE} \times I_L$$

Where:

$V_{CSH}$  = Voltage at CSH Pin in CCM

$R_{SENSE}$  = Current Sensing Resistance

$I_L$  = Inductor Current per Phase

Because the current sensing range is  $\pm 120$  mV, the output voltage range of  $V_{DROOP}$  is 0V to 0.9V.

The part of the schematic to implement the AVP for a 5V output is shown in Figure 4-16. The underlying assumption is that the current sense is done using sense resistors independent of temperature.

The sizing starts with the conditions:  $V_{DROOP} = 0$  V for  $I_{OUT} = 0$  A and  $V_{DROOP} = 600$  mV for  $I_{OUT} = I_{OUT(MAX)}$ . Depending on the voltage drop across the sense resistors at  $I_{OUT(MAX)}$ , the DROOP pin can have a value different from 600 mV, assuming that  $V_{DROOP(IOUTMAX)} = 600$  mV.

Step 1: Sizing the resistors for getting  $(1+\epsilon) \times V_{OUT}$  at  $I_{OUT} = 0$  A. Because  $V_{DROOP} = 0$  V, we have  $V_{OUT}$  according to Equation 4-21:

### EQUATION 4-21:

$$V_{OUT} = \left( 1 + \frac{R_{FBT}}{R_{FBB1} + R_{FBB2} || R_{DROOP}} \right) \times V_{REF}$$

As a first approximation, consider choosing  $R_{FBB2}$  small enough so that  $R_{FBB2} || R_{DROOP} \approx R_{FBB2}$ , and we size  $R_{FBB1}$ ,  $R_{FBB2}$  and  $R_{FBT}$  to get the correct 5.00V injection and stability.

Step 2: Sizing the resistors to have the trip of  $V_{OUT} \times 2 \cdot \epsilon$  from  $I_{OUT} = 0$  A to  $I_{OUT} = I_{OUT(MAX)}$  or from  $V_{DROOP} = 0$  V to  $V_{DROOP} = 600$  mV.

Then,

### EQUATION 4-22:

$$2\epsilon = \frac{\Delta V_{FBS}}{V_{REF}} = \frac{n_D \times V_{DROOP(MAX)}}{V_{REF}} \times \frac{R_{FBB2}}{R_{FBB2} + R_{DROOP}} \times \frac{R_{FBT}}{R_{FBT} + R_{FBB1} + R_{FBB2} || R_{DROOP}}$$

Where:  
 $n_D$  = Number of 2-Phase Controller Devices  
 $(n_D = 1, 2, 3, 4)$

If  $R_{DROOP} \gg R_{FBB2}$  in Equation 4-22, then we can simplify the equation as shown in Equation 4-23 or Equation 4-24:

### EQUATION 4-23:

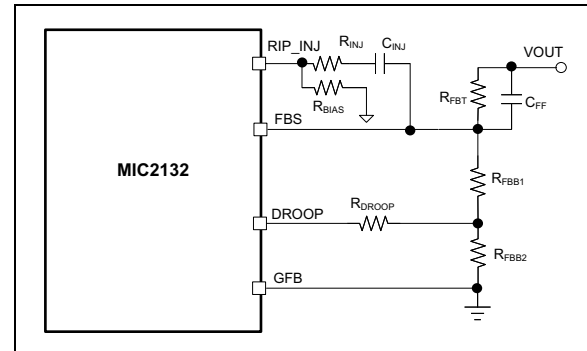
$$2\epsilon = \frac{n_D \times V_{DROOP(MAX)}}{V_{REF}} \times \frac{R_{FBB2}}{R_{FBB2} + R_{DROOP}} \times \frac{R_{FBT}}{R_{FBT} + R_{FBB1} + R_{FBB2}}$$

Or

### EQUATION 4-24:

$$R_{DROOP} = R_{FBB2} \times \left( \frac{n_D}{2\epsilon} \times \frac{V_{DROOP(MAX)}}{V_{REF}} \times \frac{R_{FBT}}{R_{FBT} + R_{FBB1} + R_{FBB2}} - 1 \right)$$

Step 3: The  $R_{FBB1}$  is slightly adjusted to get  $V_{OUT} \times (1 + \epsilon)$  for  $I_{OUT} = 0$  A. The result is in Figure 4-16.



**FIGURE 4-16:** AVP Implementation for 5V Output with 2% AVP Range for DROOP Pin Range 0V to 600 mV.

Equation 4-23 and Equation 4-24 can also have the exact solution; the main difficulty being to find standard resistors of 0.1% to respect the initial positioning of  $+ \epsilon$  for  $I_{OUT} = 0$  A and the  $2 \cdot \epsilon$  move down for  $I_{OUT(MAX)}$ .

The example above was based on temperature-independent current sensing using sense resistors. In case the bottom FET is used, the  $V_{DROOP}$  is defined as:

### EQUATION 4-25:

$$V_{DROOP} = V_{CSH} - 1.2V = 8 \times R_{DSON(LS)} \times I_L$$

Where:

$R_{DSON(LS)}$  = Low-Side MOSFET Turn-On Resistance

Considering the sensing current range of 120 mV, it results that the operating maximum voltage value is:

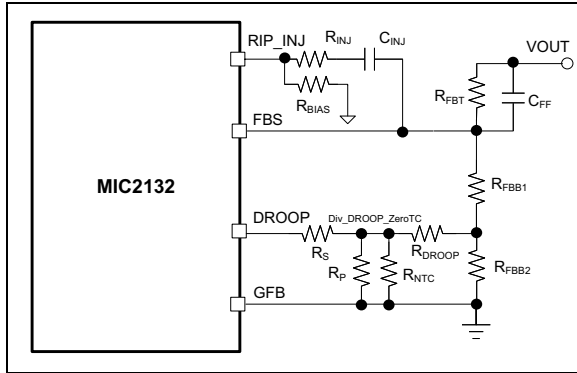
### EQUATION 4-26:

$$V_{DROOP(MAXOP)} = 120 \text{ mV} \times 8 = 0.96 \text{ V}$$

Since  $R_{DSON(LS)}$  increases to about 2x at +125°C related to the value at +25°C, it is necessary to choose  $R_{DSON} \times I_{OUT(MAX)} < 60$  mV at +25°C in order to respect the sensing range over temperature.

To desensitize the AVP related to the temperature variation of  $R_{DSON}$ , a resistance network used with an NTC resistor needs to be used, as shown in Figure 4-17 on the next page.

# MIC2132



**FIGURE 4-17:** Use of an NTC Resistance to Compensate the  $R_{DS(on)}$  Temperature Coefficient on the DROOP Pin.

The idea in Figure 4-17 is that increasing DROOP voltage with temperature at the  $I_{OUT(MAX)}$  (positive temperature coefficient) is compensated by the  $R_{NTC}$  (negative temperature coefficient) to keep the node of the divider, Div\_DROOP\_ZeroTC, constant versus temperature.

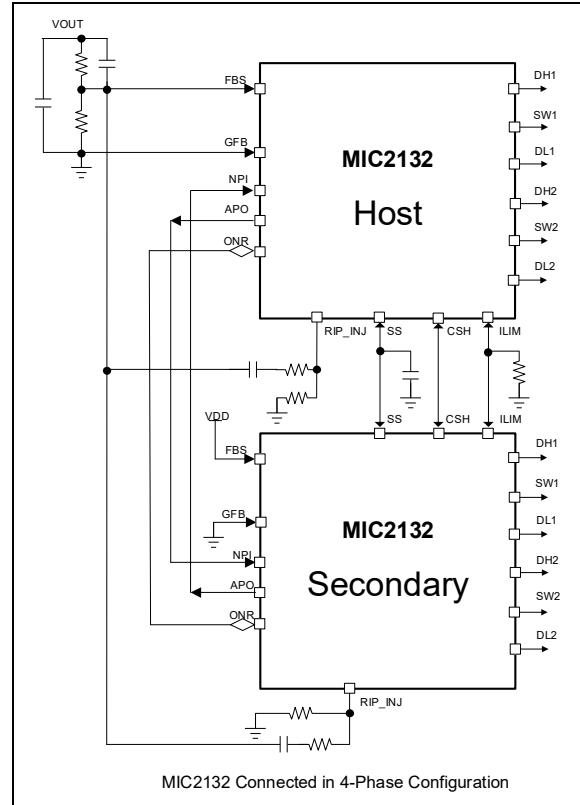
The rest of the calculations are similar to the aforementioned case where the sensing current was temperature-insensitive. In case the AVP is not necessary, a 10 k $\Omega$ , 1 nF series RC filter to ground can be used to have a reading of the filtered output current.

## 4.5.10 MULTIPHASING (STACKING)

The MIC2132 can be configured for multiphase operation of up to eight phases. The MIC2132 has four pins allocated for multiphasing. The APO pin of the host controller is connected to the NPI pin of the next secondary controller. The host and secondary CSH, ONR pins are connected together. Once the host finishes the on requests, it passes the control to the next secondary through the APO pin. The current share bus will maintain equal current sharing between host and secondary controllers.

The ONR is a bidirectional pin. The desired secondary controller's FBS pin is connected to VDD to program the controller as secondary. This will make the ONR pin of the secondary controller become input only. Secondary controllers accept ONR from the host controller and serve the on-time request.

Figure 4-18 shows two MIC2132 devices connected in a 4-phase configuration. The NPI and APO pins of the MIC2132 are connected in a daisy-chain to form a stackable power supply up to eight phases.



**FIGURE 4-18:** MIC2132 Connected in 4-Phase Configuration.

In order to get a stricter control over behavior if one member of the daisy-chain is damaged or going to be damaged, or is in short or thermal shutdown, several measures were implemented.

1. The host is the only one programming the ILIM. The secondaries are just reading the voltage on ILIM; as a common point, they do not have any programming current coming out.
2. The soft start pin is driven up with 1.2  $\mu$ A from all members of the daisy-chain. When any of the members of the daisy-chain pulls down the SS pin in case of thermal shutdown, or short circuits more than seven cycles, a new automatic restart is triggered on the falling edge of SS. Any of the daisy-chain members can keep low closed to 0 in the SS pin, and in that case, all members are in High-Z and wait until SS is released to go up. To illustrate if one member has the LDO not coming up, this will keep the SS pin in low.
3. To ensure that some timing mismatch between chips is not creating a disorderly start, the delay in the block, BiasReadyGen, is 3 ms for the host and 1.5 ms (half) for the secondaries. The 3 ms and 1.5 ms time frames are the result of the activity of a local oscillator and counter.

This way, if there is a slight difference between different chips coming up, the secondaries are ready when the host is waking up after 3 ms.

4. The logic input pin, NPI (Next Phase In), of each part in the daisy-chain has a 136 kΩ resistor to ground externally near the pin in the application. This way, if the input is floating because of a bad connection in the production line, it will be pushed to 0V, which will stop any activity from the chip to start. Also, NPI is active only on the rising edge. If it is floating and with no rising edge detected, the activity will stop.
5. When in daisy-chain, the logic pin, ONR (On Request), from the host as output is going in each secondary ONR pin configured as an input. In order to accommodate different V<sub>DD</sub> rails from different secondaries and not to inject too much current in one of the secondaries from the host, the ONR pin as logic output has a 1 kΩ pull-up resistor inside. This way, the output ONR is short-protected ~ 5 mA to ground and the strength of the injection in the V<sub>DD</sub> rail of each secondary is 2k = 1k + 1k. Special precautions are designed inside so that this small injection will not trigger latch-up.
6. Only the error amplifier of the host controller regulates the output and feedback. The secondaries are only serving the ONR coming using the logic pins, NPI and APO, in sequence. The secondaries also inject ripple in the feedback in order to allow correct phasing and regulation. All members in the daisy-chain are sharing the CSH pin to allow correct (equal) current sharing.
7. If the droop feature is required in multiphase operation, connect all the droop setting resistors from the DROOP pins of all members in the daisy-chain to the lower bottom feedback resistor to achieve load line setting as in dual phase operation.

## 4.5.11 FREQUENCY PROGRAMMING

The switching frequency per phase in CCM in two-phase operation can be programmed by [Equation 4-27](#) below:

### EQUATION 4-27:

$$R_{FREQ} = \frac{20.1 \times 10^9}{f_{SW\_PH}}$$

Where:

$R_{FREQ}$  = Resistor Connects from FREQ Pin to AGND.

## 4.5.12 THERMAL SHUTDOWN

When the junction temperature of the MIC2132 reaches +160°C or above, the buck converter goes into thermal shutdown. When the junction temperature falls below +140°C, the MIC2132 buck converter soft starts again.

## 5.0 APPLICATION INFORMATION

### 5.1 Inductor Selection

Certain values for inductance, peak and RMS currents are required to select the output inductor. The input and output voltages, as well as the inductance value, determine the peak-to-peak inductor ripple current. Generally, higher inductance values are used with higher input voltages. Larger peak-to-peak ripple currents increase the power dissipation in the inductor and MOSFETs. Larger output ripple currents also require more output capacitance to smooth out the larger ripple current. Smaller peak-to-peak ripple currents require a larger inductance value, and therefore, a larger and more expensive inductor. Higher switching frequencies allow the use of a small inductance, but increase power dissipation in the inductor core and MOSFET switching loss. A good compromise between size, loss and cost is to set the inductor ripple current to be equal to 20% of the maximum DC output current contributed per phase. The inductance value of the inductor in each phase channel is calculated by [Equation 5-1](#):

#### EQUATION 5-1:

$$L = \frac{V_{OUT} \times (Eff \times V_{IN(MAX)} - V_{OUT}) \times N_{PH}}{Eff \times V_{IN(MAX)} \times f_{SW} \times 0.2 \times I_{OUT(MAX)}}$$

Where:

- $f_{SW}$  = Switching Frequency, 500 kHz
- 0.2 = Ratio of AC Ripple Current to Maximum DC Output Current Contributed per Phase
- $V_{IN(MAX)}$  = Maximum Power Stage Input Voltage
- $N_{PH}$  = Total Number of Phases
- $Eff$  = Efficiency of the Buck Converter
- $I_{OUT(MAX)}$  = Maximum DC Output Current

The peak-to-peak inductor current ripple in each phase is:

#### EQUATION 5-2:

$$\Delta I_{L(PP)} = \frac{V_{OUT} \times (Eff \times V_{IN(MAX)} - V_{OUT})}{Eff \times V_{IN(MAX)} \times f_{SW} \times L}$$

The peak inductor current per phase is equal to the maximum average output current per phase, plus one half of the peak-to-peak inductor current ripple, as given in [Equation 5-3](#).

#### EQUATION 5-3:

$$I_{L\_PH(PK)} = I_{OUTPH(MAX)} + 0.5 \times \Delta I_{L(PP)}$$

$$I_{OUTPH(MAX)} = \frac{I_{OUT(MAX)}}{n}$$

Where:

- $I_{OUTPH(MAX)}$  = Maximum Average DC Output Current Contributed per Phase
- $I_{OUT(MAX)}$  = Maximum Output Current
- $n$  = Total Number of Phases

The RMS inductor current in each phase is used to calculate the  $I^2R$  losses in the inductor per phase.

#### EQUATION 5-4:

$$I_{L\_PH(RMS)} = \sqrt{I_{OUTPH(MAX)}^2 + \frac{\Delta I_{L(PP)}^2}{12}}$$

Maximizing efficiency requires selecting the proper core material and minimizing the winding resistance. The high-frequency operation of the MIC2132 requires the use of ferrite materials for all but the most cost-sensitive applications. Lower cost iron powder cores may be used, but the increase in core loss reduces the efficiency of the buck converter. This is especially noticeable at low output power. The winding resistance decreases efficiency at the higher output current levels. The winding resistance must be minimized, although this usually comes at the expense of a larger inductor size. The power dissipated in the inductor is equal to the sum of the core and copper losses. At higher output loads, the core losses are usually insignificant and can be ignored. At lower output currents, the core losses can be a significant contributor. Core loss information is usually available from the magnetics vendor. Copper loss in the inductor is calculated by [Equation 5-5](#):

#### EQUATION 5-5:

$$P_{INDUCTOR(Cu)} = I_{L\_PH(RMS)}^2 \times R_{WINDING}$$

The resistance of the copper wire,  $R_{WINDING}$ , increases with the temperature. The value of the winding resistance used must be at the operating temperature for accurate power dissipation estimation:

#### EQUATION 5-6:

$$R_{WINDING(HT)} = R_{WINDING(20^\circ C)} \times [1 + 0.0042 \times (T_H - T_{20^\circ C})]$$

Where:

- $T_H$  = Temperature of Wire Under Full Load
- $T_{20^\circ C}$  = Ambient Room Temperature
- $R_{WINDING(20^\circ C)}$  = Room Temperature Winding Resistance (usually specified by the manufacturer)

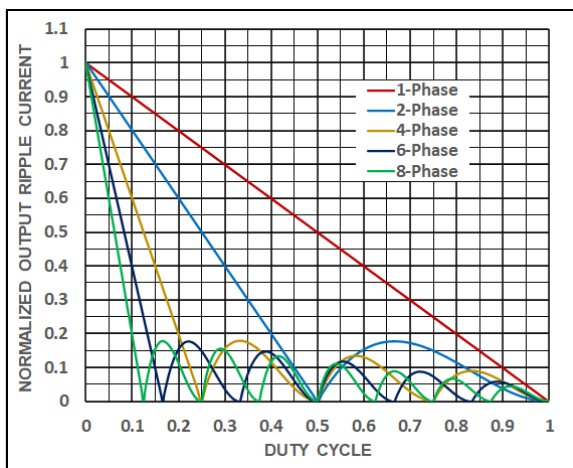


## 5.2 Output Capacitor Selection

The output capacitor is usually determined by its capacitance and Equivalent Series Resistance (ESR). Voltage and RMS current capability are two other important factors in selecting the output capacitor. Recommended capacitor types are ceramic, low-ESR aluminum electrolytic, OS-CON and POSCAP. The output capacitor's ESR is usually the main cause of the output ripple voltage in steady state, while the total output capacitance must be large enough to sustain and maintain the output voltage during load transient to meet the desired load transient output voltage requirement.

To determine the required output capacitance for a two-phase buck converter in steady state, peak-to-peak output ripple current as seen by the output capacitors must be known. The peak-to-peak output ripple current for single-phase, two-phase, four-phase, six-phase and eight-phase buck converters is shown in Figure 5-1. The graph shows that peak-to-peak output ripple current, normalized by the maximum value, is a function of the duty cycle. Since each channel is 180 degrees out of phase with the other for a two-phase buck converter, the two-phase peak-to-peak output ripple current is less than that for a single-phase converter and the ripple current effective frequency is doubled, as seen by the output capacitor. This is the ripple reduction effect of two-phase operation. In addition, at 50% duty cycle, the inductor ripple currents from each channel cancel each other and the output ripple current is close to zero.

More ripple reduction can be achieved similarly for multiphase operation by stacking MIC2132 devices, up to four devices together, for multiphase operation from four-phase up to eight-phase.



**FIGURE 5-1:** Normalized Peak-to-Peak Output Ripple Current vs. Duty Cycle.

The peak-to-peak output ripple current shown in Figure 5-1 is normalized by the maximum value, which is used as the normalizing factor for simplifying the calculation of output ripple current.

The peak-to-peak output ripple current maximum value and normalizing factor is calculated by Equation 5-7.

### EQUATION 5-7:

$$\Delta I_{OPP(MAX)} = \frac{V_{OUT}}{L \times f_{SW}}$$

The approximate peak-to-peak output ripple current of a given multiphase buck converter at a given duty cycle can be determined from the corresponding normalized value for the multiphase buck converter in Figure 5-1, multiplied by the normalizing factor, as shown in Equation 5-8.

### EQUATION 5-8:

$$\Delta I_{OPP} = \Delta I_{OPP(NORMALIZED)} \times \Delta I_{OPP(MAX)}$$

Where:

$\Delta I_{OPP(NORMALIZED)}$  = Normalized Peak-to-Peak Output Ripple Current Value for Given Multiphase Buck Converter at Given Duty Cycle in Figure 5-1

The total output ripple voltage is a combination of the ripple voltages caused by the ESR and output capacitance. The output ripple voltage of the two-phase buck converter in steady state can then be determined from Equation 5-9.

### EQUATION 5-9:

$$\Delta V_{OUT(PP)} = \sqrt{\left(\frac{\Delta I_{OPP}}{16 \times C_{OUT} \times f_{SW}}\right)^2 + (\Delta I_{OPP} \times ESR_{COUT})^2}$$

Where:

$\Delta V_{OUT(PP)}$  = Peak-to-Peak Output Ripple Voltage  
 $\Delta I_{OPP}$  = Peak-to-Peak Output Ripple Current  
 $C_{OUT}$  = Output Capacitance  
 $f_{SW}$  = Switching Frequency per Phase  
 $ESR_{COUT}$  = ESR of Output Capacitor

The minimum output capacitance required for a two-phase buck converter in steady state can be estimated by Equation 5-10.

### EQUATION 5-10:

$$C_{OUT} \geq \frac{\Delta I_{OPP}}{16 \times \Delta V_{OUT(PP)} \times f_{SW}}$$

To meet the load transient requirement, the output capacitance must also fulfill the criteria in Equation 5-11. The output capacitance value chosen must meet the criteria in both equations.

## EQUATION 5-11:

$$C_{OUT} \geq \frac{\Delta I_{LOAD}}{\Delta V_{OUT(TRANS)} \times \pi \times f_{CO}}$$

Where:

$\Delta I_{LOAD}$  = Output Load Current Step in Load Transient

$\Delta V_{OUT(TRANS)}$  = Output Voltage Change in Load Transient

$f_{CO}$  = Crossover Frequency, Equal to About  $f_{SW}/10$

The maximum value of the overall ESR of the output capacitor in steady state is calculated in [Equation 5-12](#).

## EQUATION 5-12:

$$ESR_{COUT} \leq \frac{\Delta V_{OUT(PP)}}{\Delta I_{OPP}}$$

The maximum overall ESR value of the output capacitor must also meet the load transient requirement and is calculated in [Equation 5-13](#). Then, the lower value must be chosen for the output capacitor ESR.

## EQUATION 5-13:

$$ESR_{COUT} \leq \frac{\Delta V_{OUT(TRANS)}}{\Delta I_{LOAD}}$$

As described in [Section 4.1 “Control Architecture”](#) of the MIC2132 “Functional Description”, it requires at least 20 mV peak-to-peak ripple at the FBS pin to make the  $g_m$  amplifier and the error comparator behave properly.

Also, the output voltage ripple should be in phase with the inductor current.

Therefore, the output voltage ripple caused by the output capacitor’s value should be much smaller than the ripple caused by the output capacitor’s ESR. If low-ESR capacitors, such as ceramic capacitors, are selected as the output capacitors, a ripple injection method must be applied to provide enough feedback voltage ripple. Please refer to [Section 4.4 “Ripple Injection Circuit Components Selection”](#) for more details.

The voltage rating of the output capacitor should be 25% greater than the maximum output voltage. The output capacitor RMS current is calculated in [Equation 5-14](#):

## EQUATION 5-14:

$$I_{COUT(RMS)} = \frac{\Delta I_{OPP}}{\sqrt{12}}$$

The power dissipated in the output capacitor is calculated in [Equation 5-15](#).

## EQUATION 5-15:

$$P_{DISS(COUT)} = I_{COUT(RMS)}^2 \times ESR_{COUT}$$

## 5.3 Input Capacitor Selection

In addition to high-frequency ceramic capacitors, a larger bulk capacitance, either ceramic or aluminum electrolytic, should be used to help attenuate ripple on the input and to supply current to the input during large output current transients. The input capacitor for the power stage input  $V_{IN}$  should be selected for ripple voltage at  $V_{IN}$ , capacitance, ESR, ripple current rating and voltage rating. Tantalum input capacitors may fail when subjected to high inrush currents caused by turning the input supply on. A tantalum input capacitor’s voltage rating must be at least two times the maximum input voltage to maximize reliability. Aluminum electrolytic, OS-CON and multilayer polymer film capacitors can handle the higher inrush currents without voltage derating. Due to the ripple cancellation effect of the two-phase buck converter, the input ripple voltage and ripple current are smaller than those of the single-phase converter, and the effective ripple frequency seen by the input capacitor is twice the switching frequency. The input ripple voltage depends on the input capacitor’s capacitance and ESR. The input voltage ripple can be estimated by [Equation 5-16](#).

## EQUATION 5-16:

$$\Delta V_{IN} = \frac{I_{OUT} \times \left(D - \frac{k}{n}\right) \times \left[\frac{1}{n} - \left(D - \frac{k}{n}\right)\right]}{n \times f_{SW} \times C_{IN}} + \frac{I_{OUT}}{n} \times ESR_{CIN}$$

Where:

$I_{OUT}$  = Total Output Current

$D$  = Duty Cycle per Phase

$n$  = Total Number of Phases ( $n = 2, 4, 6, 8$ )

$k$  = 0, 1, 2, 3... for  $D > k/n$  and  $k < n$

$f_{SW}$  = Switching Frequency per Phase

$C_{IN}$  = Total Input Capacitance

$ESR_{CIN}$  = Equivalent Series Resistance of Input Capacitor

The capacitance of the input capacitor can be determined in [Equation 5-17](#):

## EQUATION 5-17:

$$C_{IN} \geq \frac{I_{OUT} \times \left(D - \frac{k}{n}\right) \times \left[\frac{1}{n} - \left(D - \frac{k}{n}\right)\right]}{n \times f_{SW} \times \Delta V_{IN}}$$

Where:

$k = 0, 1, 2, 3, \dots$  for  $D > k/n$  and  $k < n$

$n$  = Total Number of Phases ( $n = 2, 4, 6, 8$ )



The ESR of the total input capacitance can be determined in [Equation 5-18](#):

**EQUATION 5-18:**

$$ESR_{CIN} \leq \Delta V_{IN} \times \frac{n}{I_{OUT}}$$

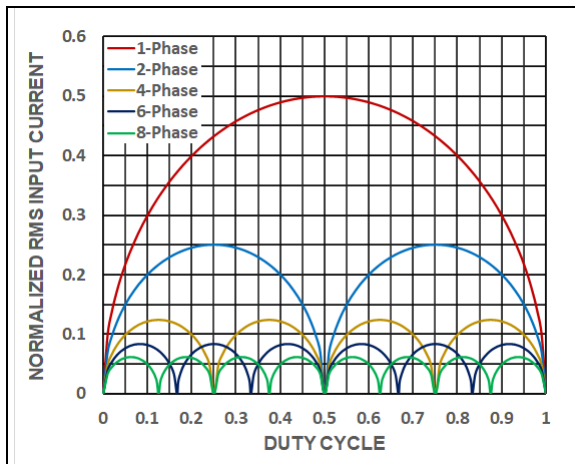
The input capacitor must be rated for the input current ripple. The rated RMS value of the input capacitor current is determined at the maximum output current. Assuming the peak-to-peak inductor current ripple is low, the RMS current rating of the input capacitor can be estimated from [Equation 5-19](#):

**EQUATION 5-19:**

$$I_{CIN(RMS)} \approx I_{OUT(MAX)} \times \sqrt{\left(D - \frac{k}{n}\right) \times \left[\frac{1}{n} - \left(D - \frac{k}{n}\right)\right]}$$

Where:  
 $I_{OUT(MAX)}$  = Maximum Output Current  
 $k = 0, 1, 2, 3, \dots$  for  $D > k/n$  and  $k < n$   
 $n$  = Total Number of Phases ( $n = 2, 4, 6, 8$ )

The graph in [Figure 5-2](#) shows the normalized RMS input capacitor current vs. duty cycle for single-phase, two-phase, four-phase, six-phase and eight-phase buck converter operation. Data are normalized to the output current.



**FIGURE 5-2:** Normalized RMS Input Capacitor Current vs. Duty Cycle.

For a given multiphase buck converter operating at duty cycle  $D$ , the input capacitor RMS current can also be determined from the graph in [Figure 5-2](#), together with [Equation 5-20](#).

**EQUATION 5-20:**

$$I_{CIN(RMS)} = I_{CINRMS(NORM)} \times I_{OUT(MAX)}$$

Where:  
 $I_{CINRMS(NORM)}$  = Normalized RMS Input Capacitor Current at given Duty Cycle for Given Multiphase Buck Converter from [Figure 5-2](#)

The power dissipated in the input capacitor can then be computed from [Equation 5-21](#):

**EQUATION 5-21:**

$$P_{DISS(CIN)} = I_{CIN(RMS)}^2 \times ESR_{CIN}$$

The voltage rating of the input capacitor must be high enough to withstand the high input voltage. The recommended voltage rating is at least 1.25 times the maximum input voltage.

## 5.4 Switch Power MOSFET Selection

The following parameters are important for MOSFET selection:

- Voltage rating
- Current rating
- On-resistance
- Total gate charge

The voltage rating for both the high-side and low-side MOSFETs in the buck converter is essentially equal to the power stage Input Voltage,  $V_{IN}$ . A safety factor of 30% should be added to the  $V_{IN(MAX)}$ , while selecting the voltage rating of the MOSFETs to account for voltage spikes due to circuit parasitic elements, as shown in [Equation 5-22](#).

**EQUATION 5-22:**

$$V_{DS(RATING)} \geq V_{IN(MAX)} \times 1.3$$

The peak switch current for both the high-side and low-side MOSFET in the buck converter is the same, and is equal to the peak inductor current in each phase, as shown in [Equation 5-23](#).

**EQUATION 5-23:**

$$I_{SWHS(PK)} = I_{SWLS(PK)} = \frac{I_{OUT(MAX)}}{n} + \frac{\Delta I_L(PP)}{2}$$

Where:  
 $I_{OUT(MAX)}$  = Maximum Output Current  
 $n$  = Total Number of Phases  
 $\Delta I_L(PP)$  = Peak-to-Peak Inductor Current per Phase

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The RMS current rating of the high-side power MOSFET in each phase channel is approximated in [Equation 5-24](#).

## EQUATION 5-24:

$$I_{SWHS(RMS)} = \frac{I_{OUT(MAX)}}{n} \times \sqrt{D_{MAX}}$$

Where:  
 $D_{MAX}$  = Maximum Duty Cycle

The maximum duty cycle of each phase channel is calculated in [Equation 5-25](#):

## EQUATION 5-25:

$$D_{MAX} = \frac{V_{OUT(MAX)}}{Eff \times V_{IN(MIN)}}$$

Where:  
 $V_{OUT(MAX)}$  = Maximum Output Voltage  
 $V_{IN(MIN)}$  = Minimum Input Voltage  
 $Eff$  = Efficiency of Buck Converter

The RMS current rating of the low-side power MOSFET in each phase channel is approximated in [Equation 5-26](#).

## EQUATION 5-26:

$$I_{SWLS(RMS)} = \frac{I_{OUT(MAX)}}{n} \times \sqrt{1 - D_{MAX}}$$

Where:  
 $D_{MAX}$  = Maximum Duty Cycle

The conduction loss of the high-side power MOSFET in each phase channel is calculated in [Equation 5-27](#).

## EQUATION 5-27:

$$P_{COND(HS)} = I_{SWHS(RMS)}^2 \times R_{DSON(HS)}$$

Where:  
 $R_{DSON(HS)}$  = High-Side MOSFET On-Resistance

The conduction loss of the low-side power MOSFET in each phase channel is calculated in [Equation 5-28](#).

## EQUATION 5-28:

$$P_{COND(LS)} = I_{SWLS(RMS)}^2 \times R_{DSON(LS)}$$

Where:  
 $R_{DSON(LS)}$  = Low-Side MOSFET On-Resistance

The switching loss of the high-side power MOSFET in each phase channel is estimated in [Equation 5-29](#).

## EQUATION 5-29:

$$P_{SWL(HS)} = V_{IN(MAX)} \times \frac{I_{OUT(MAX)}}{2n} \times (t_R + t_F) \times f_{SW}$$

$$t_R = Q_{G(HS)} \times \frac{(R_{ONDHH} + R_{G(HS)})}{V_{DD} - V_{TH(HS)}}$$

$$t_F = Q_{G(HS)} \times \frac{(R_{ONDHL} + R_{G(HS)})}{V_{TH(HS)}}$$

$$Q_{G(HS)} = 0.5 \times Q_{GSHS} + Q_{GDHS}$$

Where:  
 $t_R$  = High-Side MOSFET Turn-on Transition Time  
 $t_F$  = High-Side MOSFET Turn-off Transition Time  
 $Q_{G(HS)}$  = Switching Gate Charge of High-Side MOSFET  
 $Q_{GSHS}$  = Gate-to-Source Charge of High-Side MOSFET  
 $Q_{GDHS}$  = Gate-to-Drain Charge of High-Side MOSFET  
 $R_{ONDHH}$  = High-Side Gate Driver Pull-up Resistance  
 $R_{ONDHL}$  = High-Side Gate Driver Pull-Down Resistance  
 $R_{G(HS)}$  = Gate Resistance of High-Side MOSFET  
 $V_{TH(HS)}$  = High-Side MOSFET Gate-to-Source Threshold Voltage

The high-side MOSFET output capacitance discharge loss can be calculated in [Equation 5-30](#).

## EQUATION 5-30:

$$P_{COSS(HS)} = 0.5 \times C_{OSS(HS)} (V_{IN(MAX)})^2 \times f_{SW}$$

Where:  
 $C_{OSS(HS)}$  = High-Side MOSFET Output Capacitance

The total power dissipation of the high-side power MOSFET in each phase channel is the sum of the conduction loss, the switching loss and the MOSFET output capacitance discharge loss, as shown in [Equation 5-31](#).

## EQUATION 5-31:

$$P_{D(HS)} = P_{COND(HS)} + P_{SWL(HS)} + P_{COSS(HS)}$$

The high-side power MOSFET in each phase channel selected must be capable of handling the total power dissipation. To improve efficiency and minimize the power loss, the power MOSFET should be selected with low on-resistance and optimum gate charge.

On the other hand, the power dissipation in the low-side power MOSFET in each phase channel is mainly contributed to by the conduction loss. There is no switching loss for the low-side MOSFET in the buck converter, since the body diode of the low-side MOSFET is forward-biased before the turn-on, and after the turn-off of the low-side MOSFET, which makes the voltage across the low-side MOSFET equal to the body diode's forward voltage during the turn-on and turn-off transition.

Apart from the conduction loss, low-side MOSFET body diode forward conduction loss, body diode reverse recovery loss and low-side MOSFET output capacitance discharge loss also contribute to the power dissipation in the low-side power MOSFET in each phase channel.

The low-side MOSFET body diode forward conduction loss during dead time is calculated by [Equation 5-32](#).

### EQUATION 5-32:

$$P_{BDDT(LS)} = \frac{2 \times I_{OUT(MAX)}}{n} \times V_{F(BD)} \times t_{DT} \times f_{SW}$$

Where:

$V_{F(BD)}$  = Forward Voltage of Low-Side MOSFET Body Diode

$t_{DT}$  = Dead Time, which is about 20 ns

The low-side MOSFET body diode reverse recovery loss is calculated by [Equation 5-33](#).

### EQUATION 5-33:

$$P_{BDQRR(LS)} = V_{IN(MAX)} \times Q_{RR(BDLS)} \times f_{SW}$$

Where:

$Q_{RR(BDLS)}$  = Reverse Recovery Charge of Low-Side MOSFET Body Diode

The low-side MOSFET output capacitance discharge loss can be calculated in [Equation 5-34](#).

### EQUATION 5-34:

$$P_{COSS(LS)} = 0.5 \times C_{OSS(LS)} (V_{IN(MAX)})^2 \times f_{SW}$$

Where:

$C_{OSS(LS)}$  = Low-Side MOSFET Output Capacitance

The total power dissipation of the low-side power MOSFET in each phase channel is estimated in [Equation 5-35](#).

### EQUATION 5-35:

$$P_{D(LS)} = P_{COND(LS)} + P_{BDDT(LS)} + P_{BDQRR(LS)} + P_{COSS(LS)}$$

Since low-side MOSFETs can be accidentally turned on by the high dV/dt signal at switching node, low-side MOSFETs with high  $C_{GS}/C_{GD}$  ratio and low internal gate resistance should be chosen to minimize the effect of dV/dt induced turn-on.

## 5.5 Bootstrap Capacitor

The MIC2132 device's high-side gate drive circuits are designed to switch the N-Channel external MOSFETs. The [Functional Block Diagram](#) shows two internal bootstrap diodes and each one is between the PVDD and BST pins of each phase channel. These circuits supply energy to the high-side gate drive circuits with one for each phase. A low-ESR ceramic capacitor should be connected between the BST pin and the SW pin of each phase channel (refer to the "[Typical Application Circuit](#)"). The bootstrap capacitors between the BST and the SW pins,  $C_{BST1}$  and  $C_{BST2}$ , are charged while the respective low-side MOSFET is turned on. When the respective high-side MOSFET driver is turned on, energy from  $C_{BSTx}$  is used to turn the MOSFET on. A minimum of 0.1  $\mu$ F low-ESR ceramic capacitor is recommended between the BSTx and SWx pins. The required value of  $C_{BSTx}$  can be calculated using [Equation 5-36](#).

### EQUATION 5-36:

$$C_{BSTx} = \frac{Q_{G(HS)}}{\Delta V_{CBSTx}}$$

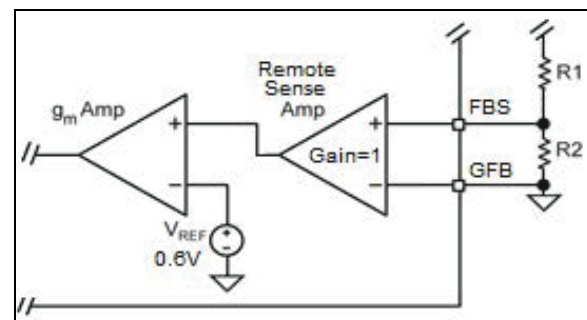
Where:

$Q_{G(HS)}$  = Gate Charge of High-Side MOSFET in Each Phase

$\Delta V_{CBSTx}$  = Voltage Drop Across  $C_{BST}$  in Each Phase, Generally 50 mV to 100 mV

## 5.6 Setting Output Voltage

The MIC2132 requires two resistors to set the output voltage, as shown in [Figure 5-3](#).



**FIGURE 5-3:** Voltage-Divider Configuration.

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The output voltage is determined by [Equation 5-37](#).

## EQUATION 5-37:

$$V_{OUT} = V_{REF} \times \left(1 + \frac{R1}{R2}\right)$$

Where:

$$V_{REF} = 0.6V$$

A typical value of R1 can be between 3 kΩ and 10 kΩ. If R1 is too large, it may allow noise to be introduced into the voltage feedback loop. If R1 is too small, it decreases the efficiency of the buck converter, especially at light loads. After R1 is selected, R2 can be calculated using the formula found in [Equation 5-38](#).

## EQUATION 5-38:

$$R2 = \frac{V_{REF} \times R1}{V_{OUT} - V_{REF}}$$

## 5.7 AVP Droop Load Line Resistance

The AVP droop load line resistance can be calculated using [Equation 5-39](#).

## EQUATION 5-39:

$$R_{LOADLINE} = \frac{\Delta V_{OUT(DROOP)}}{\Delta I_{L(PK)}} \\ = \frac{4 \times R_{SENSE}}{1 + \frac{R_{DROOP}}{R_{FBB2}}} \times \left(1 - \frac{V_{REF}}{V_{OUT}}\right) \times \frac{V_{OUT}}{V_{REF}}$$

Where:

$\Delta V_{OUT(DROOP)}$  = Change in Output Voltage with Load

$\Delta I_{L(PK)}$  = Total Change in Peak Inductor Current for All Phases for a Given Change in Load Current

$R_{SENSE}$  = Current Sense Resistance

$V_{REF}$  = Reference Voltage (0.6V typical)

$V_{OUT}$  = Output Voltage

$R_{DROOP}$  = Resistance of Droop Setting Resistor Connected at the DROOP Pin

$R_{FBB2}$  = Lower Bottom Feedback Resistance Value

## 5.8 Power Dissipation in MIC2132

The MIC2132 features two Low-Dropout (LDO) regulators to supply power at the PVDD pin from either VIN or EXTVDD, depending on the voltage at the EXTVDD pin. PVDD powers the MOSFET drivers and the VDD pin powers the internal circuitry and is recommended to connect to PVDD through a low-pass filter. In the applications where the output voltage is 5V and above (up to 14V), it is recommended to connect EXTVDD to the output to reduce the power dissipation

in the MIC2132, in order to reduce the MIC2132 junction temperature and to improve system efficiency. The power dissipation in the MIC2132 depends on the internal LDO being in use, gate charge of the external MOSFETs and switching frequency. The power dissipation and the junction temperature of the MIC2132 can be estimated using [Equation 5-40](#), [Equation 5-41](#) and [Equation 5-42](#).

Power dissipation in the MIC2132 is calculated in [Equation 5-40](#) when EXTVDD is not used.

## EQUATION 5-40:

$$P_{IC} = V_{IN} \times (I_{G(TOTAL)} + I_Q)$$

$$I_{G(TOTAL)} = (Q_{G(HS1)} \times Q_{G(LS1)} + Q_{G(HS2)} + Q_{G(LS2)})f_{SW}$$

Where:

$I_{G(TOTAL)}$  = Total Average Gate Drive Current for All Phases

$I_Q$  = Quiescent Current of MIC2132

$Q_{G(HS1)}, Q_{G(LS1)}$  = Gate Charge of High-Side and Low-Side MOSFETs in Phase 1

$Q_{G(HS2)}, Q_{G(LS2)}$  = Gate Charge of High-Side and Low-Side MOSFETs in Phase 2

Power dissipation in the MIC2132 is calculated in [Equation 5-41](#) when EXTVDD is used.

## EQUATION 5-41:

$$P_{IC} = V_{EXTVDD} \times (I_{G(TOTAL)} + I_Q)$$

Where:

$V_{EXTVDD}$  = Voltage at EXTVDD Pin  
(4.7V ≤  $V_{EXTVDD}$  ≤ 14V typically)

$I_{G(TOTAL)}$  = Total Average Gate Drive Current for All Phases

$I_Q$  = Quiescent Current of MIC2132

The junction temperature of the MIC2132 can be estimated using [Equation 5-42](#).

## EQUATION 5-42:

$$T_J = P_{IC} \times \theta_{JA} + T_A$$

Where:

$T_J$  = Junction Temperature of MIC2132

$T_A$  = Ambient Temperature

$P_{IC}$  = Power Dissipation of MIC2132

$\theta_{JA}$  = Junction-to-Ambient Thermal Resistance of MIC2132 (34°C/W typical)

The maximum recommended operating junction temperature for the MIC2132 is +125°C. Using the output voltage of the same switching converter when it is between 4.7V (typical) and 14V, as the voltage at the EXTVDD pin, significantly reduces the power dissipation inside the MIC2132. This reduces the junction temperature rise as further illustrated.

For a typical case of  $V_{IN} = 36V$ ,  $V_{OUT} = 5V$ ,  $I_{G(TOTAL)} = 20\text{ mA}$ ,  $I_Q = 5\text{ mA}$  and a maximum ambient temperature of  $T_A = +85^\circ\text{C}$  when the EXTVDD is not used, the MIC2132 junction temperature is calculated as shown in [Equation 5-43](#).

**EQUATION 5-43:**

$$P_{IC} = 36V \times (20\text{ mA} + 5\text{ mA})$$

$$P_{IC} = 0.9W$$

$$T_J = 0.9W \times 34^\circ\text{C}/W + 85^\circ\text{C}$$

$$T_J = 115.6^\circ\text{C}$$

When the EXTVDD is used and the 5V output of the MIC2132 buck converter is used as the input to the EXTVDD pin, the MIC2132 junction temperature is calculated as shown in [Equation 5-44](#). The junction temperature is reduced significantly, from +115.6°C to +89.3°C when the EXTVDD is used.

**EQUATION 5-44:**

$$P_{IC} = 5V \times (20\text{ mA} + 5\text{ mA})$$

$$P_{IC} = 0.125W$$

$$T_J = 0.125W \times 34^\circ\text{C}/W + 85^\circ\text{C}$$

$$T_J = 89.3^\circ\text{C}$$

## 5.9 Thermal Measurements

It is a good idea to measure the IC's case temperature to make sure it is within its operating limits. Although this might seem an elementary task, it is easy to get false results. The most common mistake is to use the standard thermal couple that comes with a thermal meter. This thermal couple wire gauge is large, typically 22 gauge, and behaves like a heatsink, which results in a lower case temperature measurement.

There are two methods of temperature measurement: using a smaller thermal couple wire or using an infrared thermometer. If a thermal couple wire is used, it must be constructed of 36 gauge wire or higher (smaller wire size) to minimize the wire heatsinking effect. In addition, the thermal couple tip must be covered in either thermal grease or thermal glue to ensure that the thermal couple junction makes good contact with the case of the IC. Wherever possible, an infrared thermometer is recommended. The measurement spot size of most infrared thermometers is too large for an accurate reading on a small form factor IC. However, an IR thermometer with a 1 mm spot size is a good choice for measuring the hottest point on the case. An optional stand can be used to make it easy to hold the beam on the IC for long periods of time. In addition, a more advanced, convenient and accurate infrared thermal camera can be used, although such equipment is much more expensive.

## 6.0 PCB LAYOUT GUIDELINES

**Note:** To minimize EMI and output noise, follow these layout recommendations.

PCB layout is critical to achieve reliable, stable and efficient performance. A ground plane is required to control EMI and minimize the inductance in power, signal and return paths. Use star ground technique between AGND and PGND, and minimize trace length for high-current paths.

Follow these guidelines to ensure proper operation of the MIC2132 two-phase buck converter.

### 6.1 Integrated Circuit

- The 2.2  $\mu\text{F}$  ceramic capacitor, which is connected to the VDD pin, must be located right at the IC. The VDD pin is very noise-sensitive, so the placement of the capacitor is critical. Use wide traces to connect to the VDD, PVDD and PGND pins.
- Connect a 2.2  $\mu\text{F}$  ceramic capacitor to the EXT VDD pin, which must be located right at the IC.
- Connect the Analog Ground pin (AGND) directly to the ground planes. Do not route the AGND pin to the PGND pad on the top layer.
- Use thick traces and minimize trace length for the input and output power lines.
- Keep the signal and power grounds separate, and connected at only one location.

### 6.2 Input Capacitor

- Use parallel input capacitors to minimize effective ESR and ESL of the input capacitor.
- Place input capacitors next to the high-side power MOSFETs for each phase channel.
- Place the input capacitors on the same side of the board and as close to the IC as possible.
- Connect the  $V_{\text{IN}}$  supply to the VIN pin through a 1.2 $\Omega$  resistor and connect a 1  $\mu\text{F}$  ceramic capacitor from the VIN pin to the PGND pin. Keep both the VIN pin and GND connections short.
- Place several vias to the ground plane, close to the input capacitors' ground terminal.
- Use either X7R or X5R dielectric input ceramic capacitors. Do not use Y5V or Z5U-type capacitors.
- Do not replace the ceramic input capacitor with any other type of capacitor. Any type of capacitor can be placed in parallel with the input capacitor.
- In hot-plug applications, use an electrolytic bypass capacitor to limit the overvoltage spike seen on the input supply when power is suddenly applied.

### 6.3 Inductor

- Keep the inductor connection to the switch node (SW1, SW2) short.
- Do not route any digital lines underneath or close to the inductor.
- Keep the switch node (SW1, SW2) away from the Feedback (FBS) pin.
- Connect the CSPx pin and CSNx pin directly to the drain and source of the low-side power MOSFET, respectively, and route the CSP and CSN traces together for each phase channel to accurately sense the voltage across the low-side MOSFET to achieve accurate current sensing.
- To minimize noise, place a ground plane under the inductor.
- The inductor can be placed on the opposite side of the PCB with respect to the IC. There should be sufficient vias on the power traces to conduct high current between the inductor and the IC and output load. It does not matter whether the IC or inductor is on the top or bottom, as long as there is enough heatsink and air flow to keep the power components within their temperature limits. Place the input and output capacitors on the same side of the board as the IC.

### 6.4 Output Capacitor

- Use a wide trace to connect the output capacitor ground terminal to the input capacitor ground terminal.
- The feedback trace should be separate from the power trace and connected as close as possible to the output capacitor. Sensing a long high-current load trace can degrade the DC load regulation.

### 6.5 MOSFETs

- MOSFET gate drive traces must be short and wide. The ground plane should be the connection between the MOSFET source and PGND.
- Choose a low-side MOSFET with a high  $C_{\text{GS}}/C_{\text{GD}}$  ratio and a low internal gate resistance to minimize the effect of  $dV/dt$  inducted turn-on.
- Use a 4.5V  $V_{\text{GS}}$  rated MOSFET. Its higher gate threshold voltage is more immune to glitches than a 2.5V or 3.3V rated MOSFET.

### 6.6 $V_{\text{OUT}}$ Remote Sense

- The remote sense traces must be routed close together or on adjacent layers to minimize noise pickup. The traces should be routed away from the switch node, inductors, MOSFETs and other high  $dV/dt$  or  $di/dt$  sources.

### 6.7 RC Snubber

- Place the RC snubber on either side of the board and as close to the SW pin as possible.

## 7.0 PACKAGING INFORMATION

### 7.1 Package Marking Information



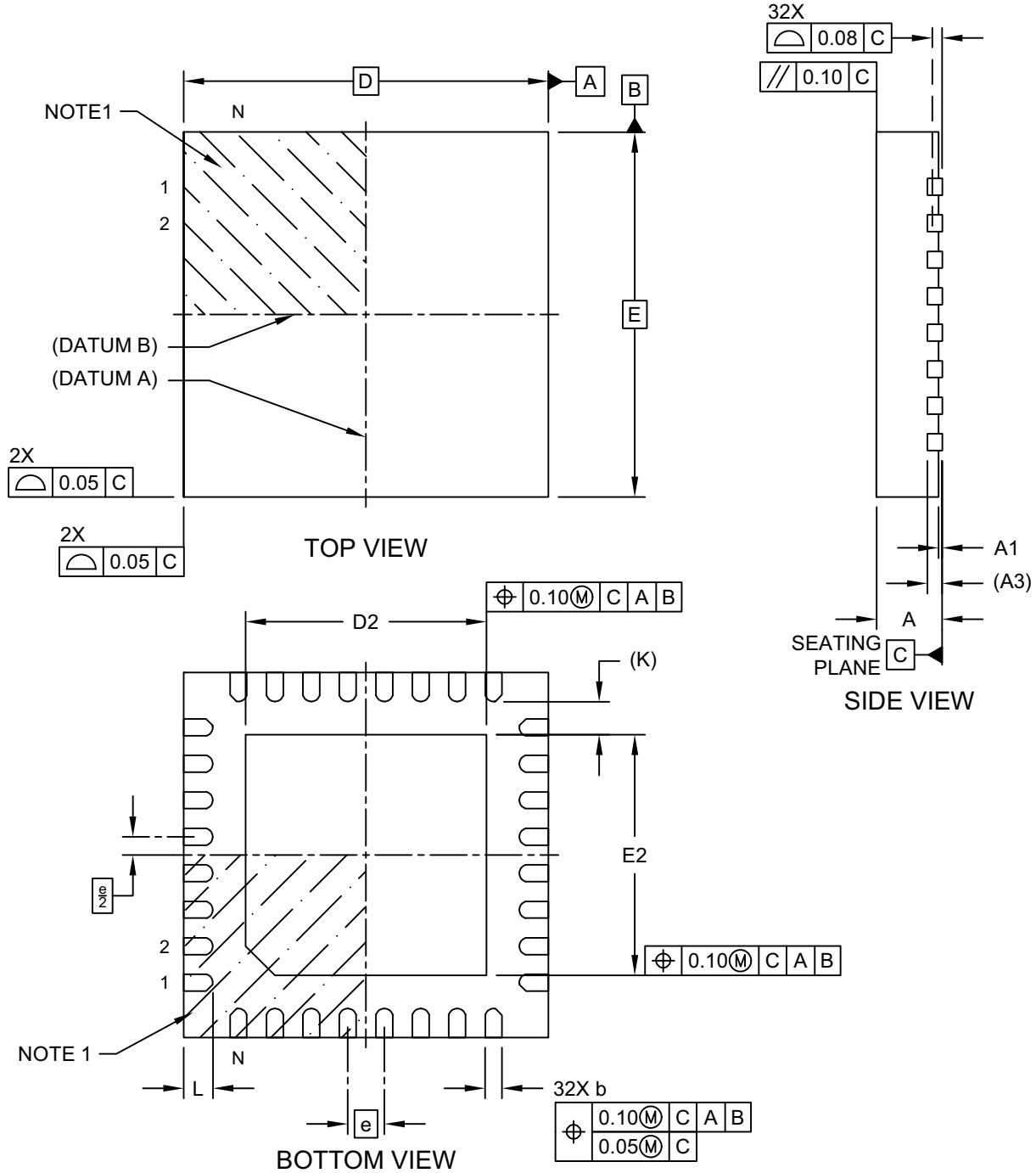
<b>Legend:</b>	XX...X	Product Code or Customer-specific information
	Y	Year code (last digit of calendar year)
	YY	Year code (last 2 digits of calendar year)
	WW	Week code (week of January 1 is week '01')
	NNN	Alphanumeric traceability code
	(e3)	Pb-free JEDEC designator for Matte Tin (Sn)
	*	This package is Pb-free. The Pb-free JEDEC designator (e3) can be found on the outer packaging for this package.

**Note:** In the event the full Microchip part number cannot be marked on one line, it will be carried over to the next line, thus limiting the number of available characters for customer-specific information. Package may or not include the corporate logo.

# MIC2132

## 32-Lead Very Thin Quad Flat, No Lead Package (QLA) - 5x5x0.9 mm Body [VQFN] With 3.3 mm Exposed Pad

**Note:** For the most current package drawings, please see the Microchip Packaging Specification located at <http://www.microchip.com/packaging>

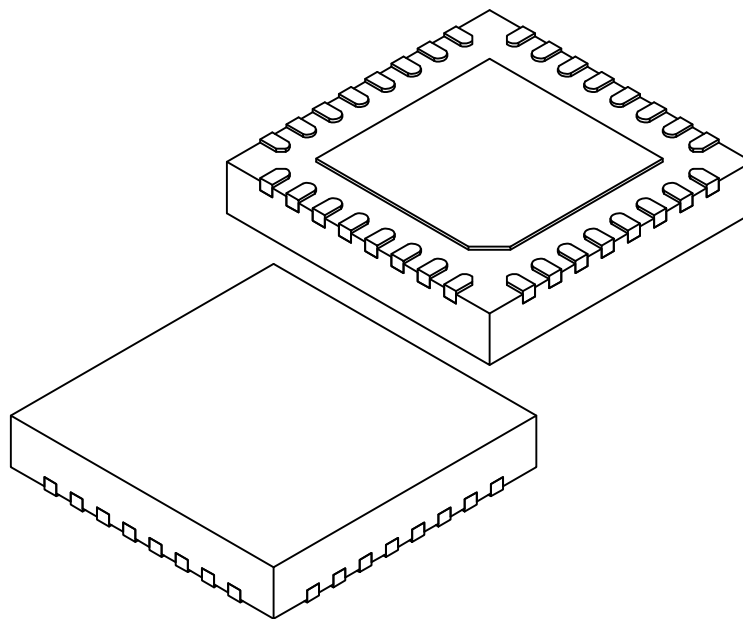


Microchip Technology Drawing C04-1285 Rev A Sheet 1 of 2



## 32-Lead Very Thin Quad Flat, No Lead Package (QLA) - 5x5x0.9 mm Body [VQFN] With 3.3 mm Exposed Pad

**Note:** For the most current package drawings, please see the Microchip Packaging Specification located at <http://www.microchip.com/packaging>



		MILLIMETERS		
Units		MIN	NOM	MAX
Dimension Limits				
Number of Terminals	N	32		
Pitch	e	0.50 BSC		
Overall Height	A	0.80	0.85	0.90
Standoff	A1	0.00	0.02	0.05
Terminal Thickness	A3	0.203 REF		
Overall Length	D	5.00 BSC		
Exposed Pad Length	D2	3.25	3.30	3.35
Overall Width	E	5.00 BSC		
Exposed Pad Width	E2	3.25	3.30	3.35
Terminal Width	b	0.18	0.23	0.28
Terminal Length	L	0.35	0.40	0.45
Terminal-to-Exposed-Pad	K	0.45 REF		

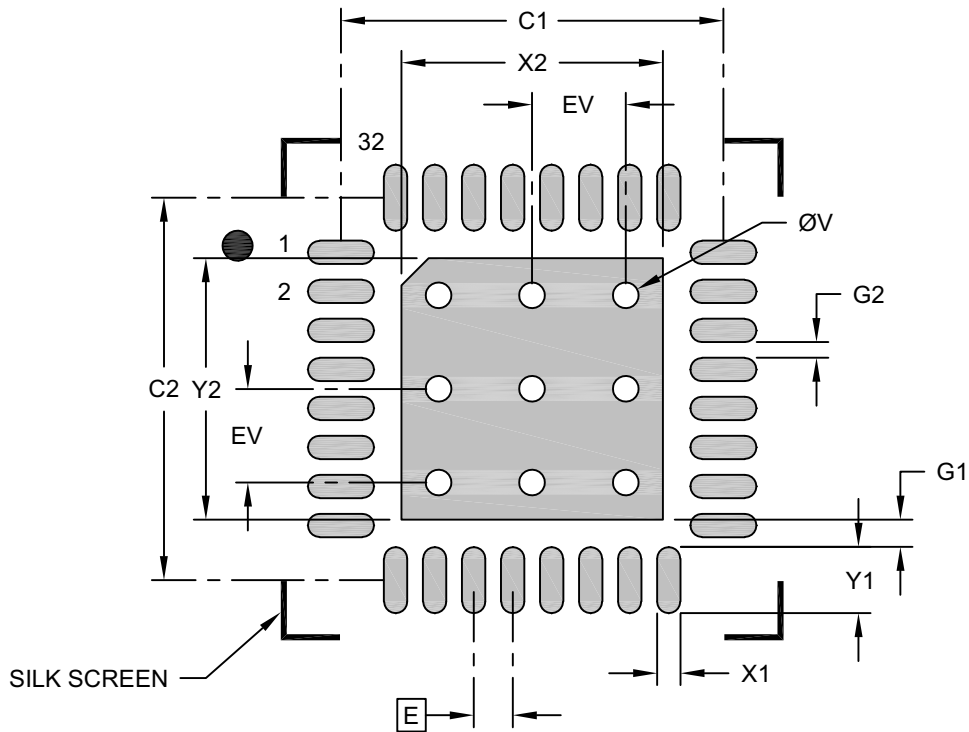
**Notes:**

- Pin 1 visual index feature may vary, but must be located within the hatched area.
- Package is saw singulated
- Dimensioning and tolerancing per ASME Y14.5M  
 BSC: Basic Dimension. Theoretically exact value shown without tolerances.  
 REF: Reference Dimension, usually without tolerance, for information purposes only.

# MIC2132

## 32-Lead Very Thin Quad Flat, No Lead Package (QLA) - 5x5x0.9 mm Body [VQFN] With 3.3 mm Exposed Pad

**Note:** For the most current package drawings, please see the Microchip Packaging Specification located at <http://www.microchip.com/packaging>



### RECOMMENDED LAND PATTERN

Dimension Limits	Units	MILLIMETERS		
		MIN	NOM	MAX
Contact Pitch	E	0.50 BSC		
Optional Center Pad Width	X2			3.35
Optional Center Pad Length	Y2			3.35
Contact Pad Spacing	C1	4.90		
Contact Pad Spacing	C2	4.90		
Contact Pad Width (X32)	X1			0.30
Contact Pad Length (X32)	Y1			0.85
Contact Pad to Center Pad (X32)	G1	0.35		
Contact Pad to Contact Pad (X28)	G2	0.20		
Thermal Via Diameter	V		0.33	
Thermal Via Pitch	EV		0.20	

**Notes:**

- Dimensioning and tolerancing per ASME Y14.5M  
BSC: Basic Dimension. Theoretically exact value shown without tolerances.
- For best soldering results, thermal vias, if used, should be filled or tented to avoid solder loss during reflow process

Microchip Technology Drawing C04-3285 Rev A

## APPENDIX A: REVISION HISTORY

### Revision A (April 2022)

- Initial release of this document.

# MIC2132

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NOTES:

## PRODUCT IDENTIFICATION SYSTEM

To order or obtain information, e.g., on pricing or delivery, refer to the factory or the listed sales office.

<u>PART NO.</u>	<u>X</u>	<u>XX</u>	<u>[-XX]<sup>(1)</sup></u>
Device	Junction Temperature Range	Package Type	Media Type
<b>Device:</b>	MIC2132:	75V Dual Phase, Advanced COT Buck Controller, Stackable for Multiphase Operation	
<b>Junction Temperature Range:</b>	Y	= -40°C to +125°C, RoHS-Compliant	
<b>Package:</b>	ML	= 32-Lead, 5 x 5 mm VQFN	
<b>Media Type:</b>	(Blank) TR	= 73/Tube = 3300/Reel	

<b>Examples:</b>	
a) MIC2132YML:	75V, Dual Phase, Advanced COT Buck Controller, Stackable for Multiphase Operation, -40°C to +125°C Junction Temperature Range, 32-Lead 5 mm x 5 mm VQFN Package, 73/Tube
b) MIC2132YML-TR:	75V, Dual Phase, Advanced COT Buck Controller, Stackable for Multiphase Operation, -40°C to +125°C Junction Temperature Range, 32-Lead 5 mm x 5 mm VQFN Package, 3300/Reel

**Note 1:** Tape and Reel identifier only appears in the catalog part number description. This identifier is used for ordering purposes and is not printed on the device package. Check with your Microchip Sales Office for package availability with the Tape and Reel option.

# MIC2132

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NOTES:

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